

University of Alabama | Chemical and Biological Engineering



Chemistry Effects on the Electrodeposition of Superconducting Metals and Alloys



Qiang Huang
<http://eeml.ua.edu>

10/11/2022

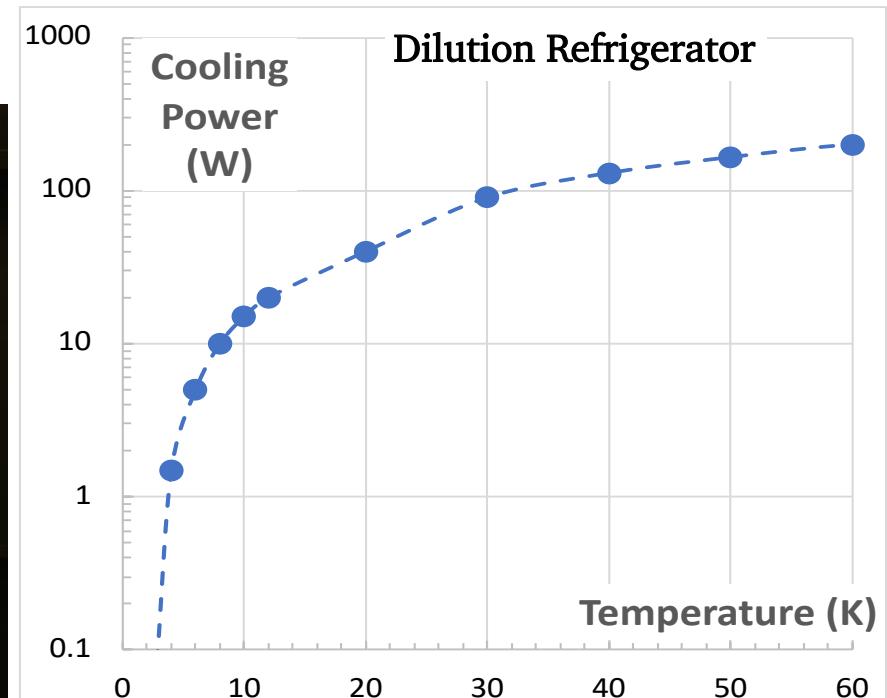
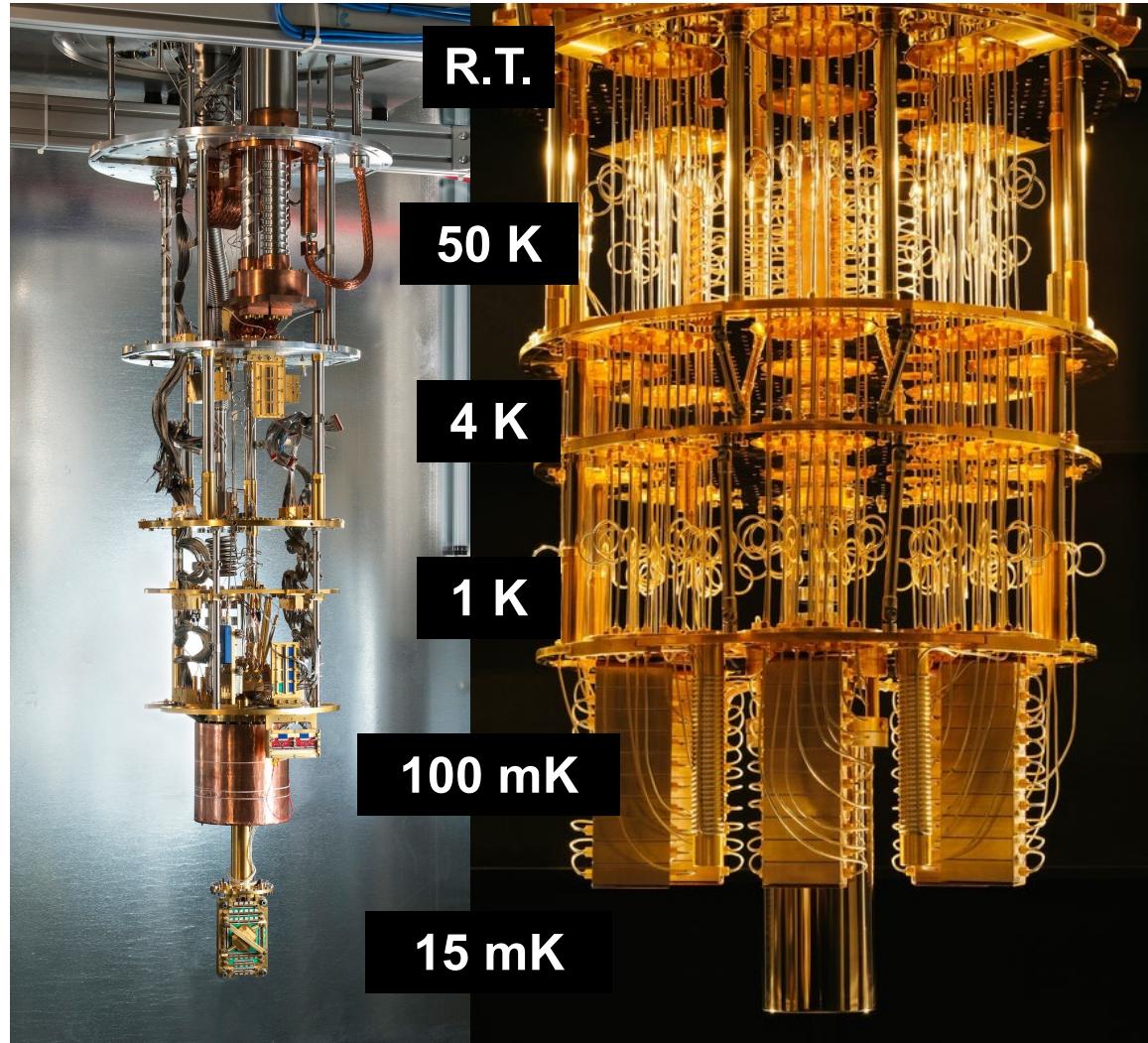
Qiang Huang

September 19, 2022

Acknowledgement

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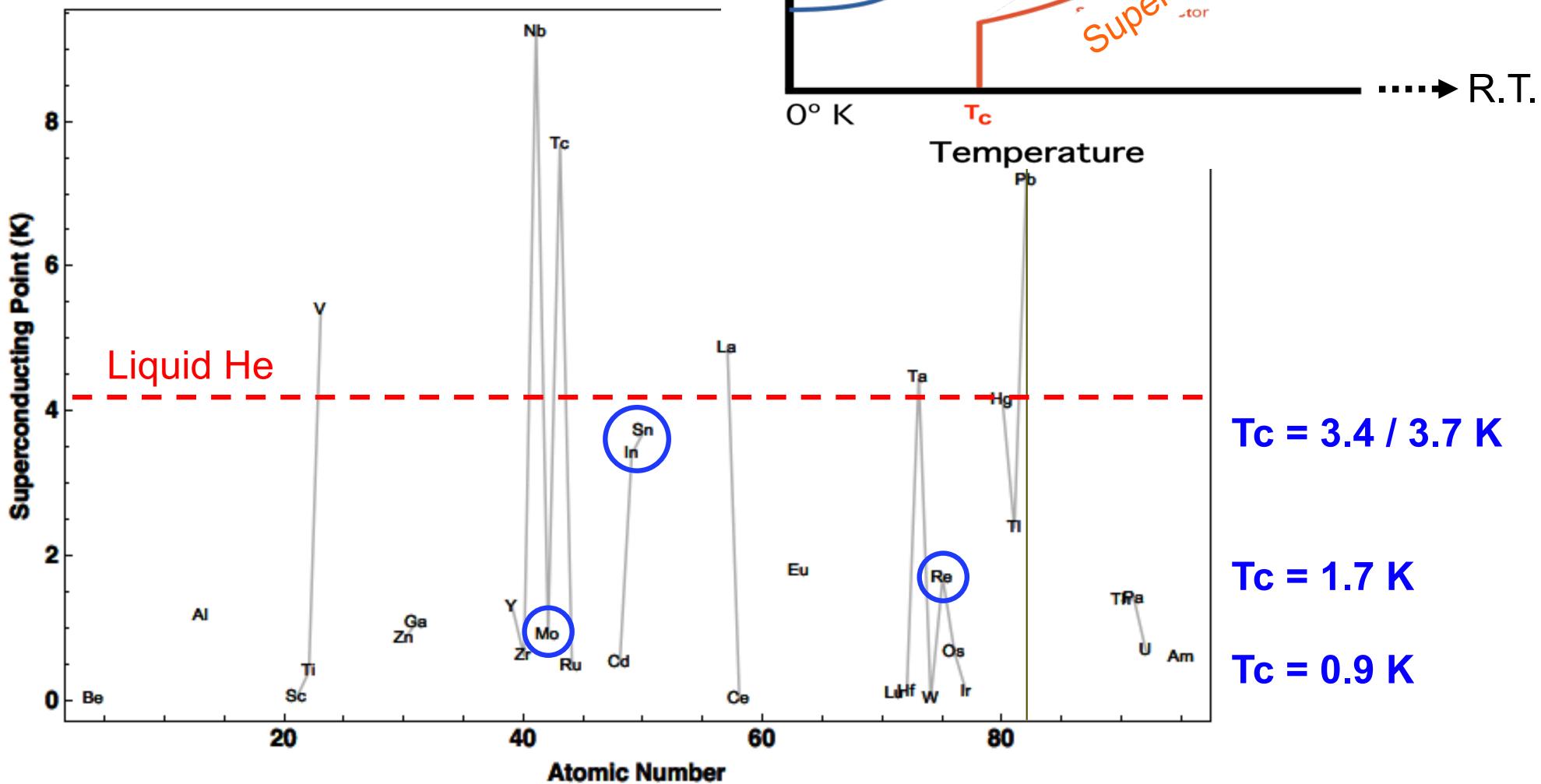
Superconductive Circuits



S. W. van Sciver, Helium Cryogenics, 2011.

Superconductors with different transition temperatures are needed for applications in different temperature zones.

Superconductors

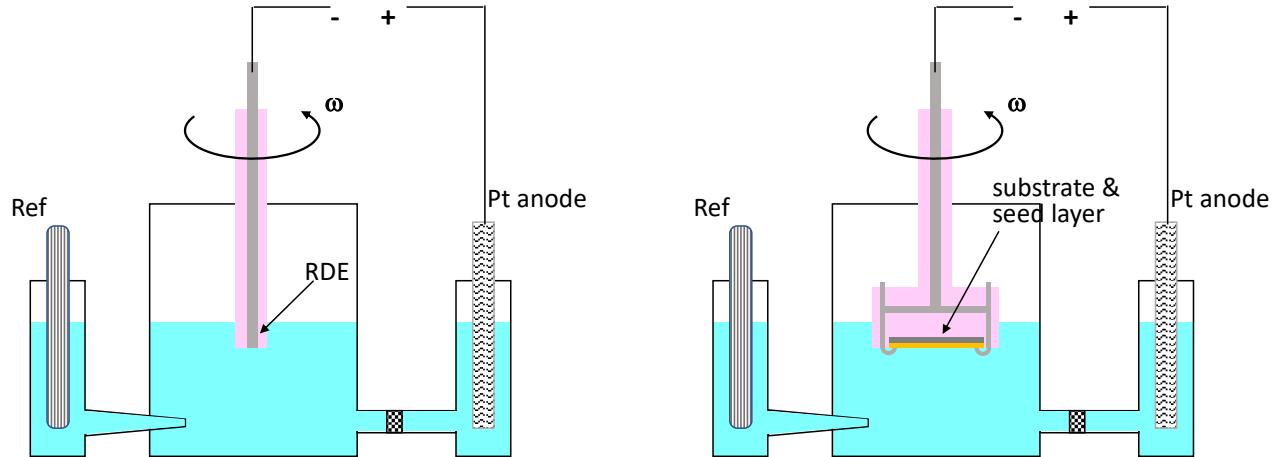


Electrodeposition of Sn

- SnSO_4 0.15 M

- H_2SO_4 1 M

- Organic additives



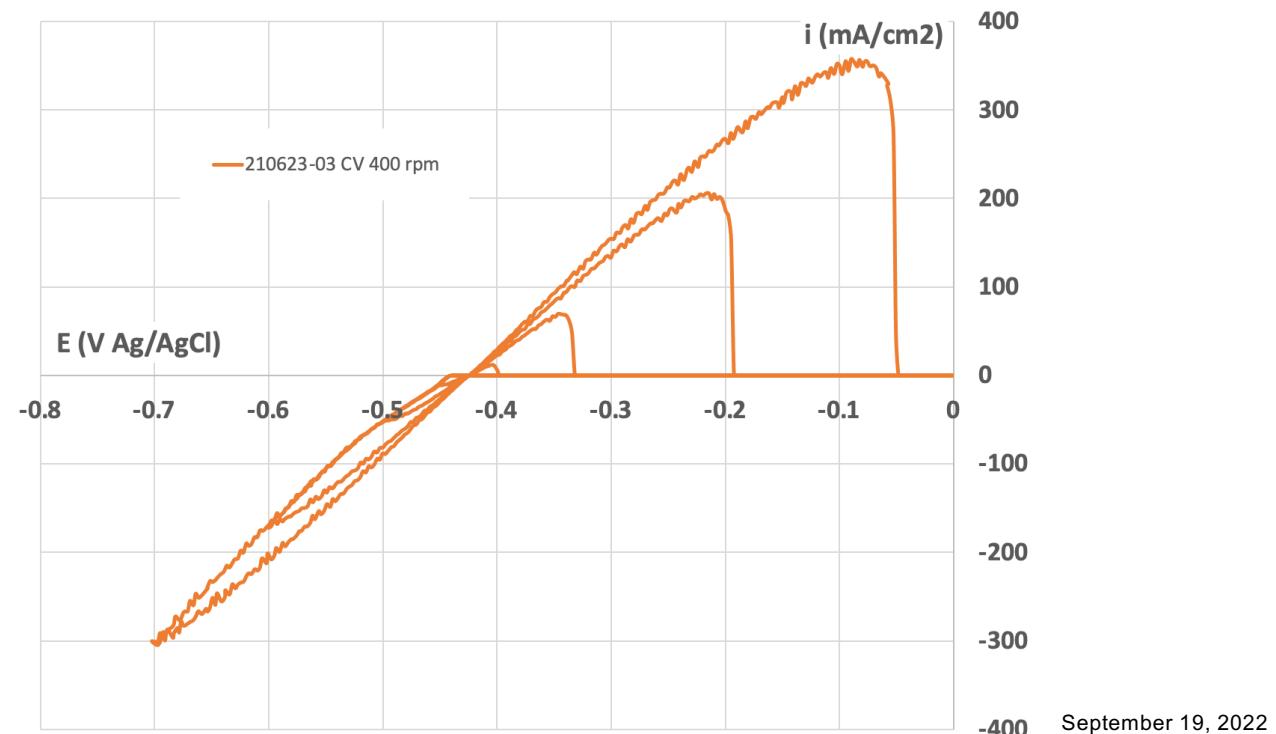
- Pt RDE

- Sn anode

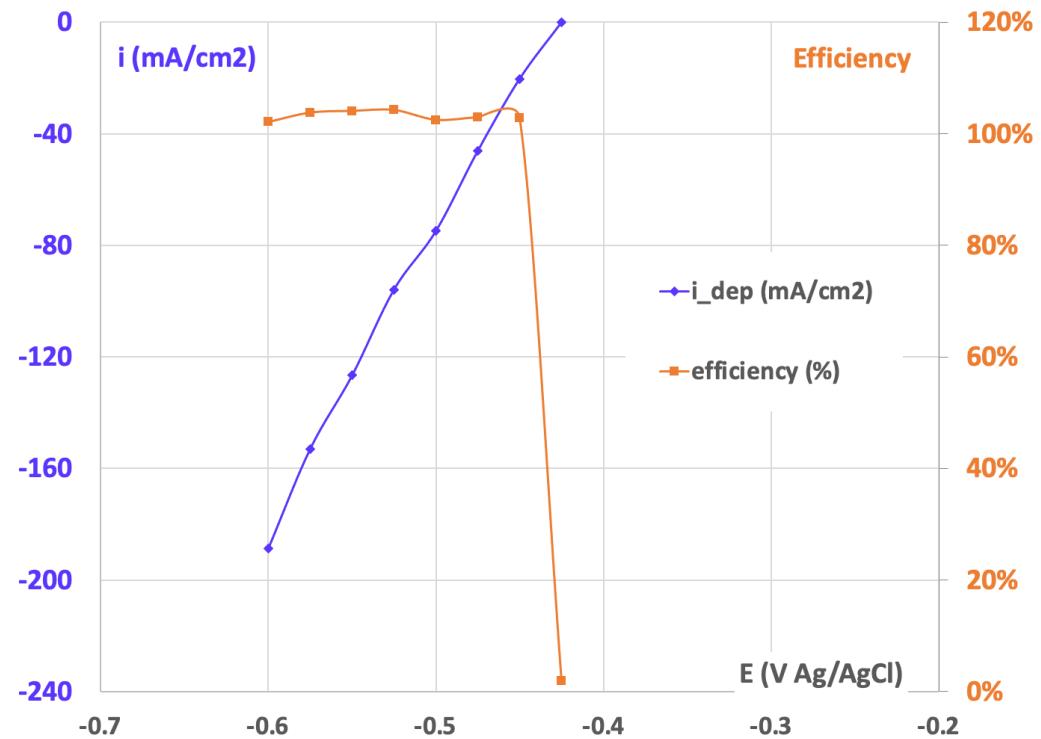
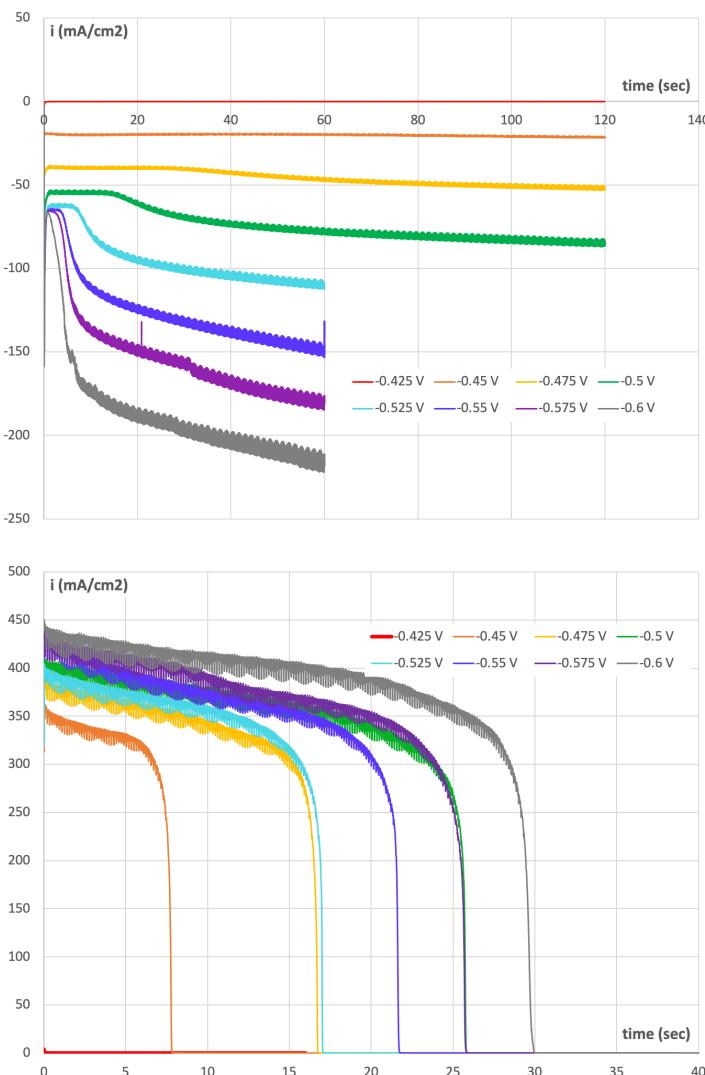
- Ag/AgCl REF

- Si / SiO_2 / Ti / (100 nm) Au

- Characterization : XRF, SEM, XRD, PPMS



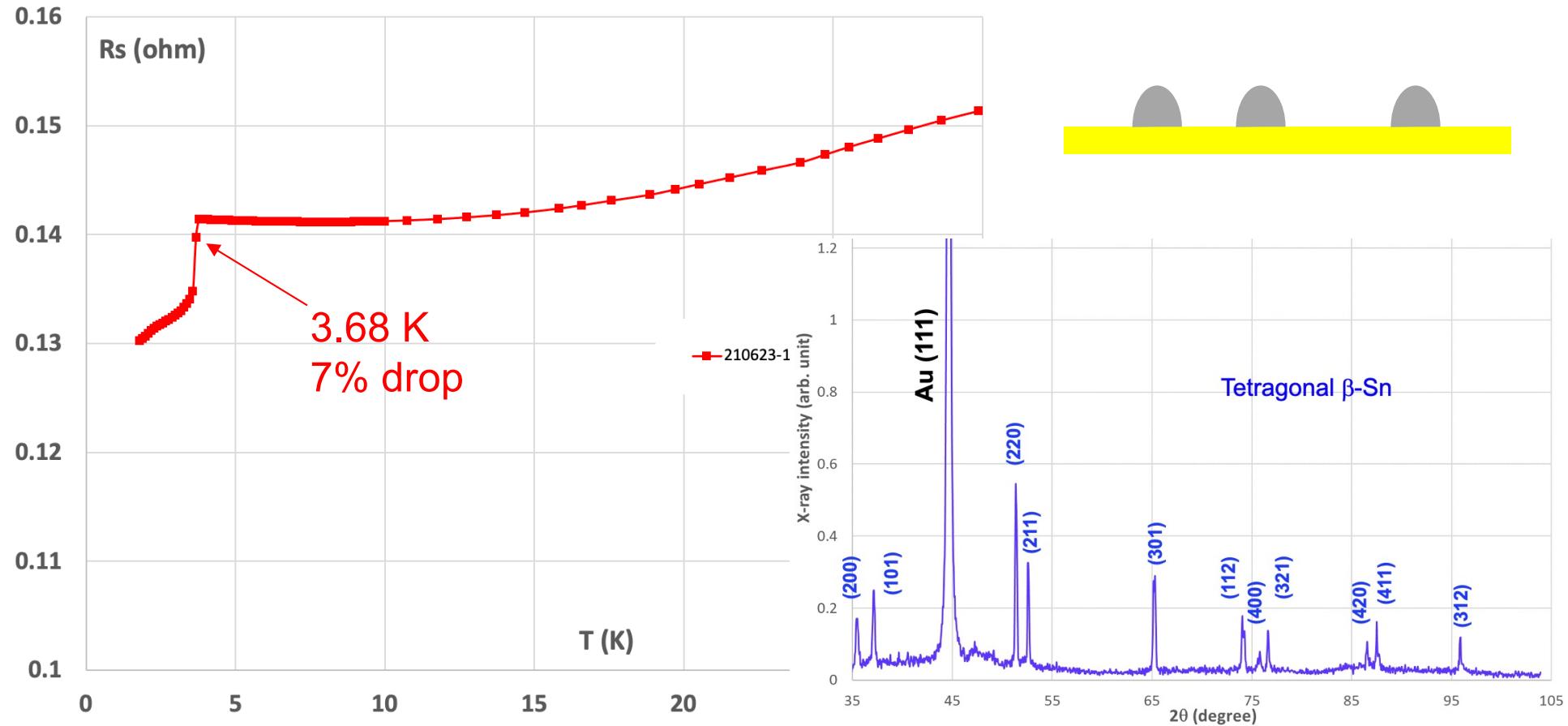
Efficiency of deposition



- Current efficiency of Sn deposition remains at 100% even at high current density up to -200 mA/cm^2 , due to low HER exchange current (on Sn).
- Deposition current = deposition rate

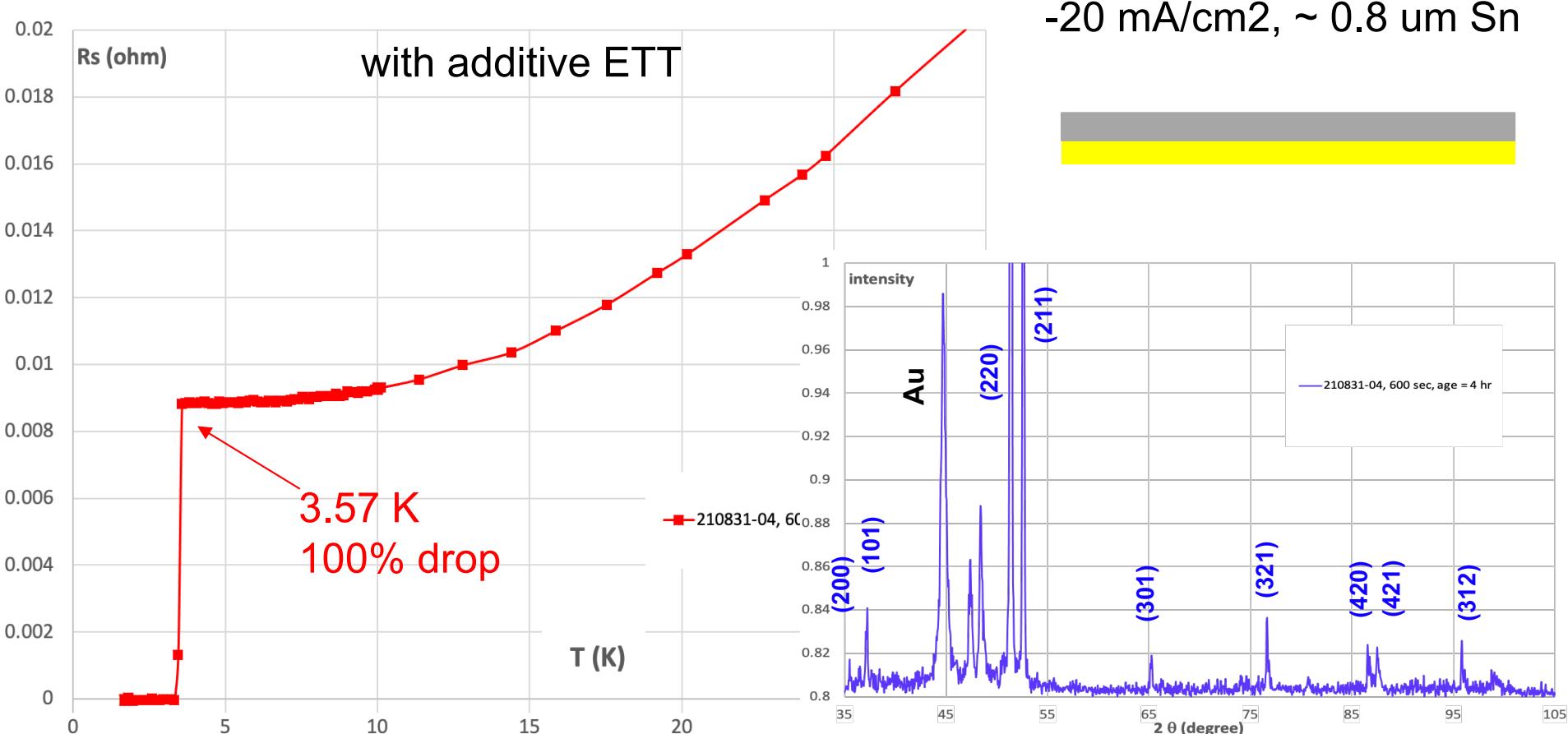
T_c of deposited Sn (on Si/Au pattern)

-50 mA/cm², "1.5" um Sn



- Sharp but small (<10%) resistance drop observed at 3.7 K, with a slow transition tail.
- The resistance does not drop to 0 – suggesting a non-continuous / non-coalescent Sn film despite of a thickness of 1.5 um.
- Tetragonal β-Sn was obtained, with T_c = 3.7 K.

T_c of deposited Sn with additive ETT (on Si/Au pattern)



- Sharp superconducting transition observed at 3.7 K when Sn is deposited with ETT.
- A continuous Sn film is deposited with suppressing additives.

Ethylenediamine tetrakis (propoxylate-block-ethoxylate) tetrol

ETT 3600

Average MW = 3,600

Tetronic 701

Cloud point 18 C (1wt% aqueous solution)

More hydrophobic

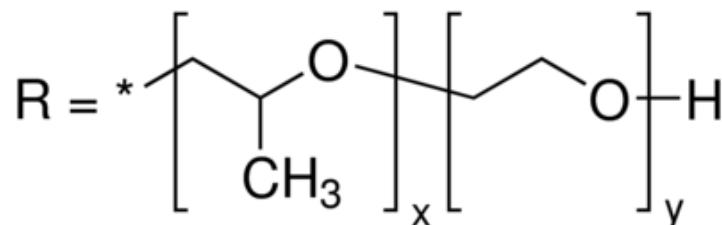
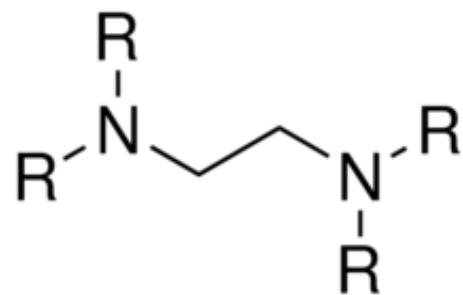
ETT 7200

Average MW = 7,200

Tetronic 90R4

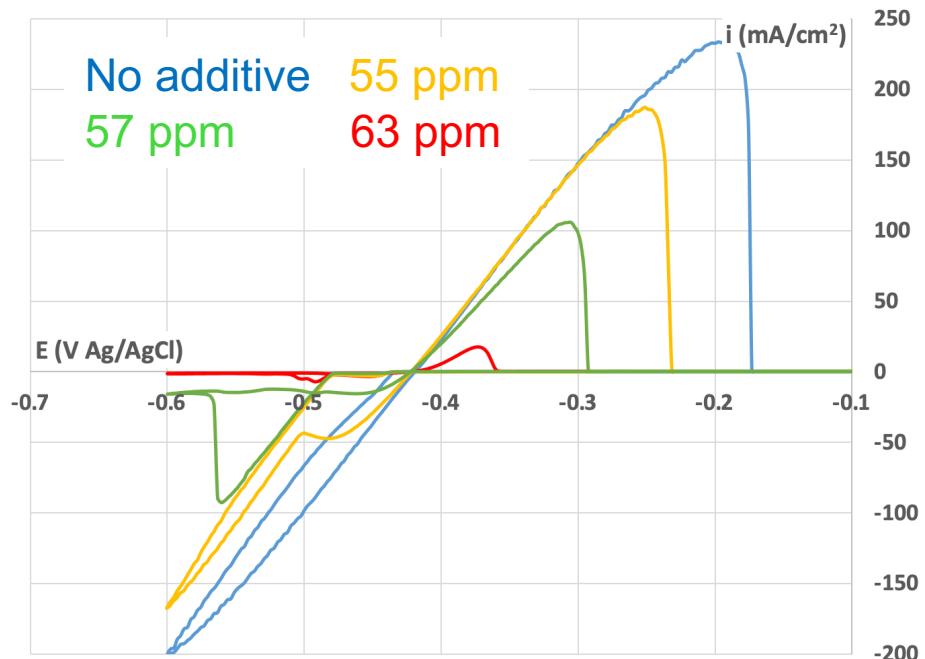
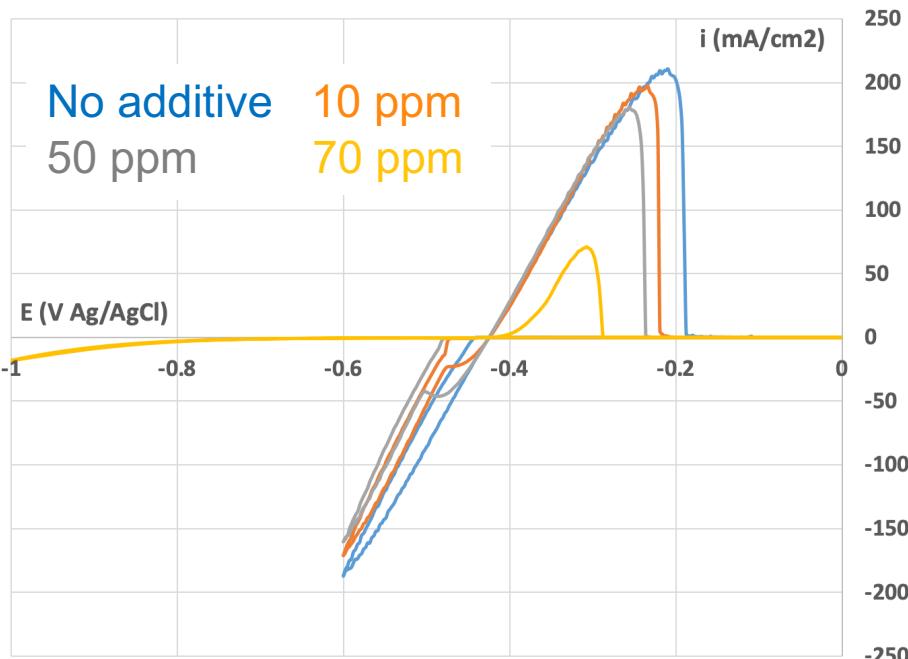
Cloud point 43 C (1wt% aqueous solution)

More hydrophilic



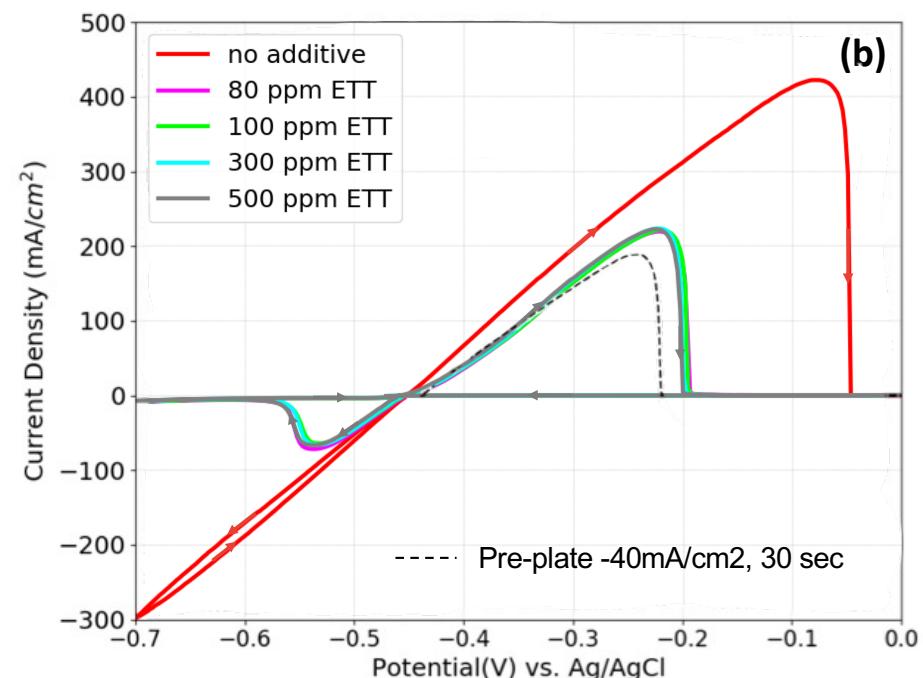
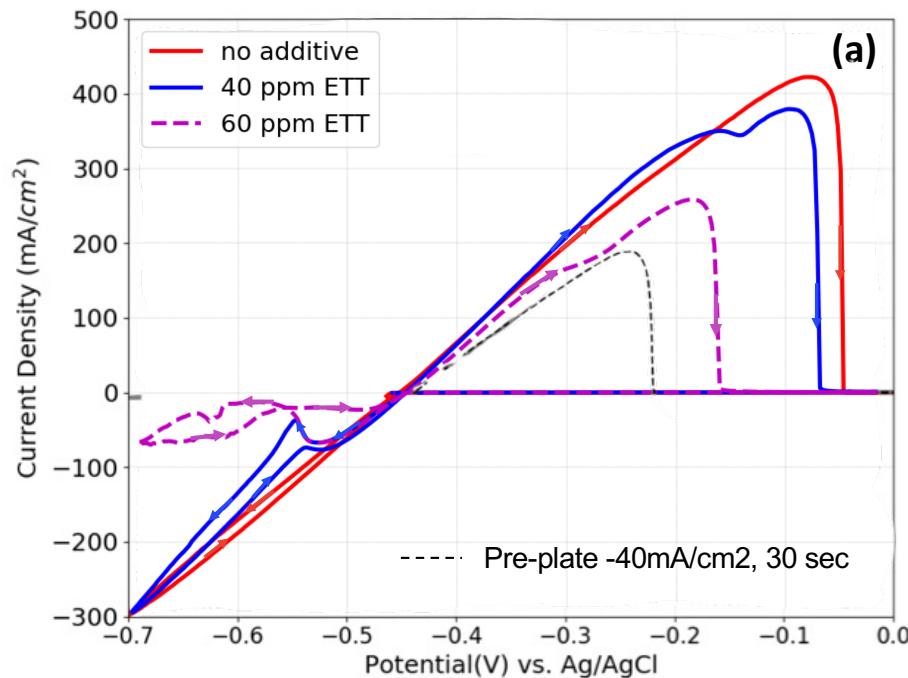
$(PPG)_x$ $(PEG)_y$

ETT 3600 – concentration effect



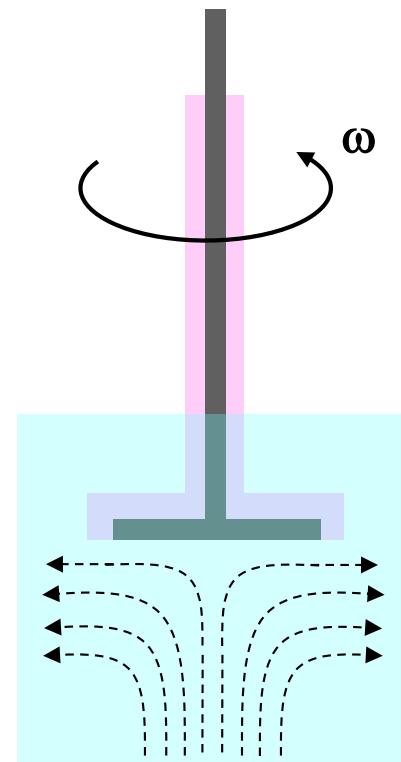
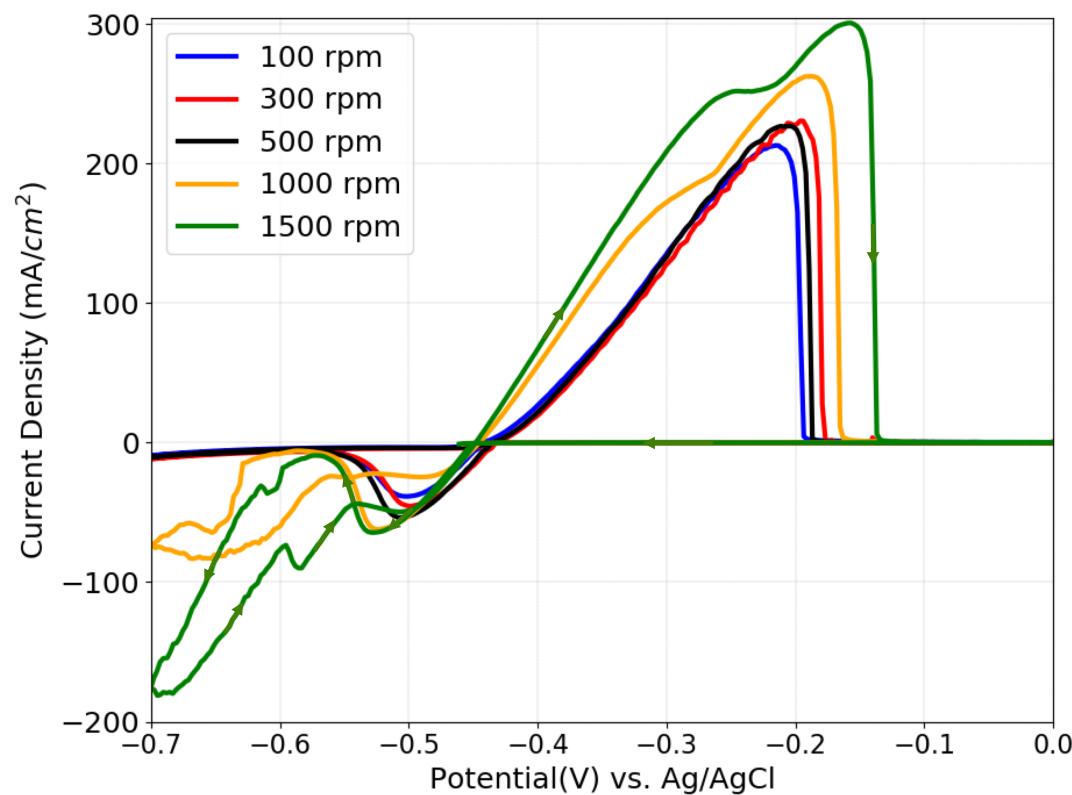
- ETT 3.6k suppresses Sn deposition, and the suppression saturates at about 60 ppm.
- This suppression, when saturated, completely shuts off the Sn deposition.

ETT 7200 – concentration effect



- ETT 7.2k suppresses Sn deposition, and this suppression saturates at 80 ppm.
- Small amount of Sn deposition still occurs with a current peak, even at suppression saturation, suggesting weaker suppression with more hydrophilic additives, despite of higher molecular weight.

Agitation effect

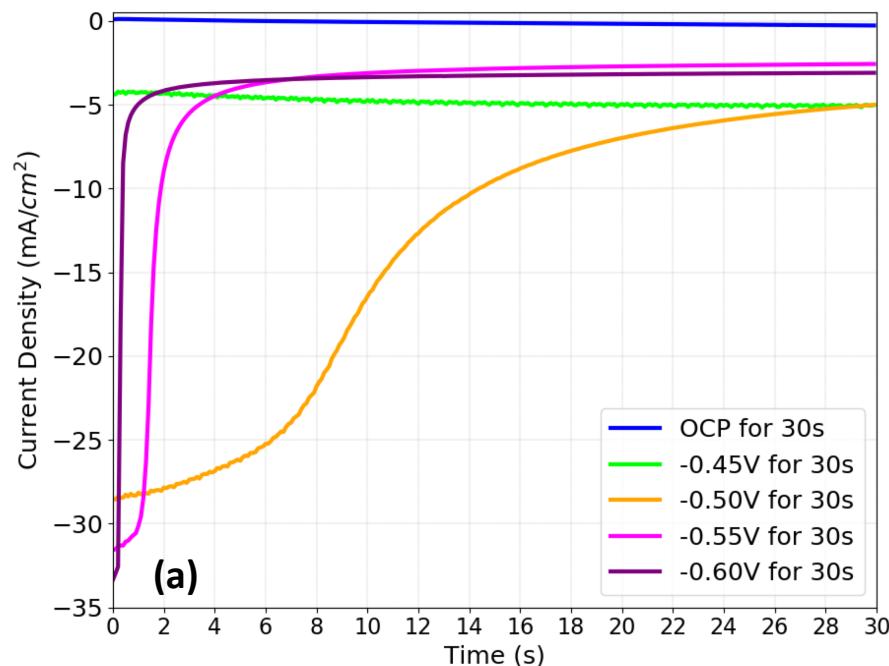


- Suppression is weakened by stronger agitation.
- A weak (physical) adsorption suggested.
- Not a diffusion limited process with consumption at surface.

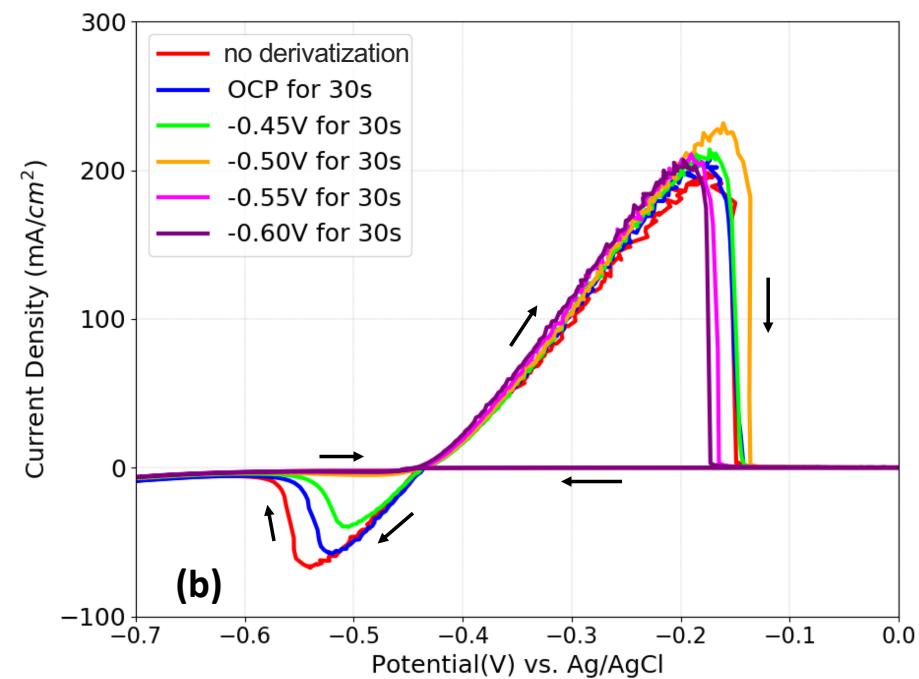
- Y. Hu, et al, *Electrochim. Acta.*, 2022.

Pre-derivatization study

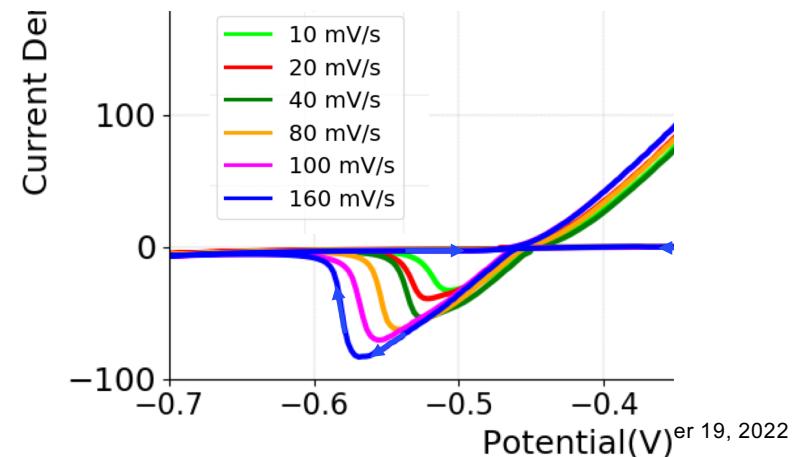
30 s derivatization at different voltage



CV after derivatization



- The time-dependent adsorption of ETT is also potential dependent.
- The higher current peak at higher scan rate results from both the time effect and potential effect.



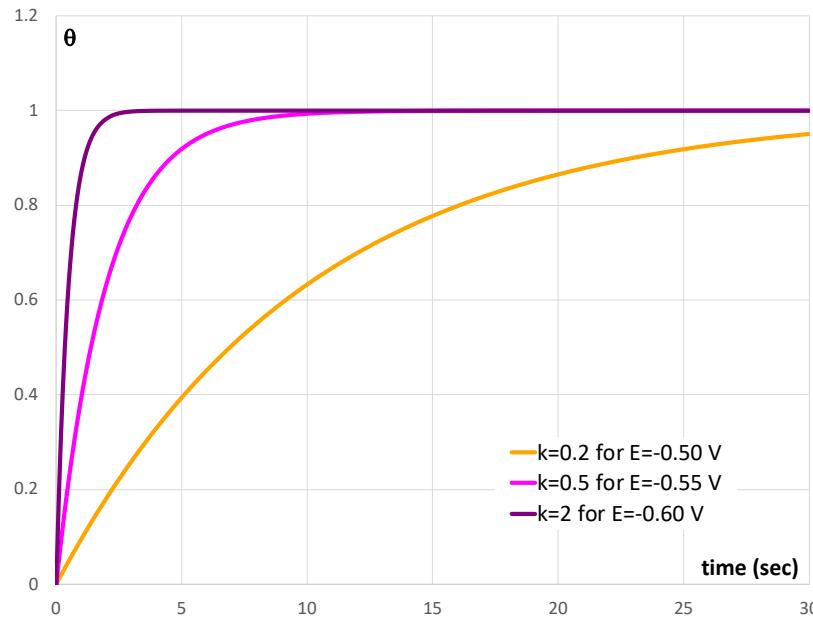
Adsorption rate

- **Langmuir isotherm**

$$\frac{d\theta}{dt} = k_{ad} \cdot (1 - \theta) - k_d \cdot \theta$$

$$\frac{d(1 - \theta)}{(1 - \theta)} = -k_{ad} \cdot dt$$

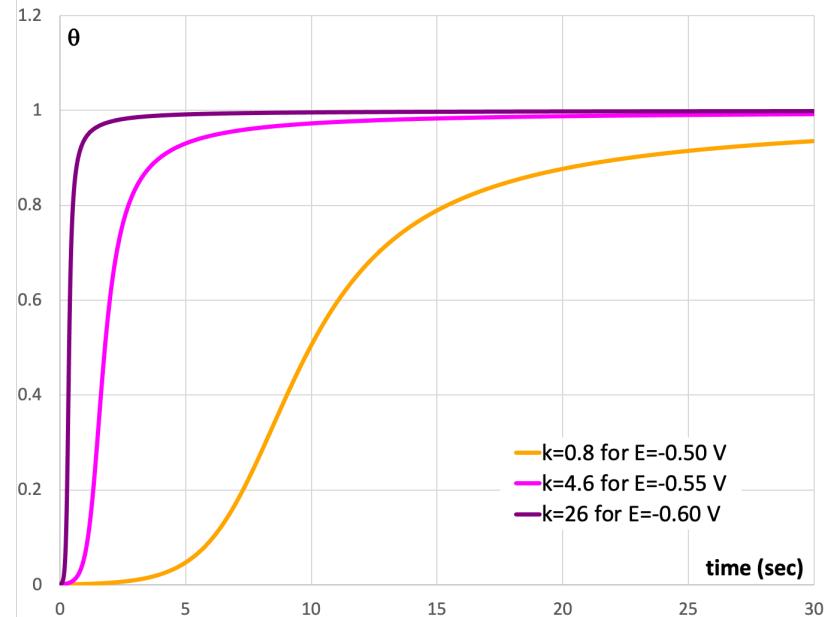
$$\theta = 1 - e^{-k_{ad} \cdot t}$$



- **Coverage dependent**

$$\frac{d\theta}{dt} = k \cdot \theta^m \cdot (1 - \theta)^n - desorption$$

- **The S-shape curve suggests dependency on coverage in addition to empty fraction.**

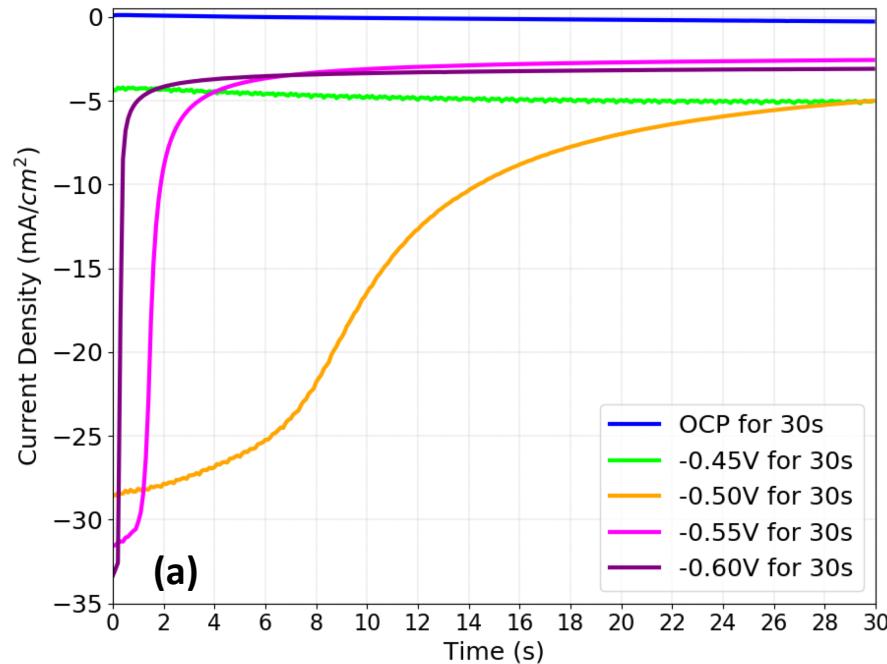


Adsorption rate

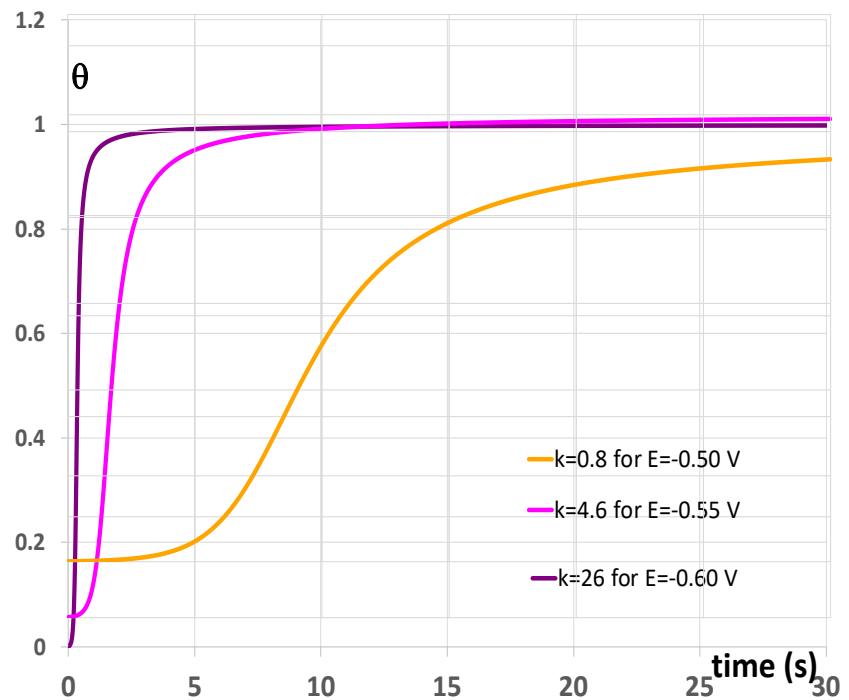
- Coverage dependent

$$\frac{d\theta}{dt} = k \cdot \theta^m \cdot (1 - \theta)^n - \text{desorption}$$

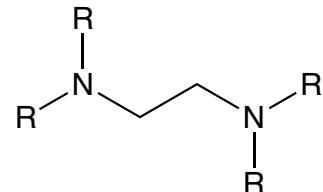
30 s derivatization at different voltage



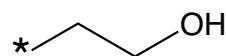
Computed θ with $m=1$, $n=2$



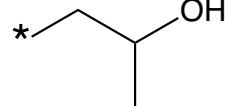
Critical functional groups



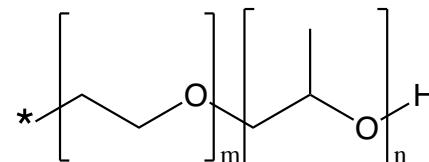
Ethylenediamine



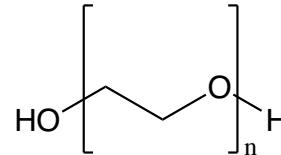
N, N, N', N' - Tetrakis (2-hydroxyethyl) ethylenediamine



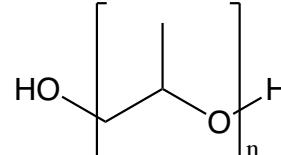
N, N, N', N' - Tetrakis (2-hydroxypropyl) ethylenediamine



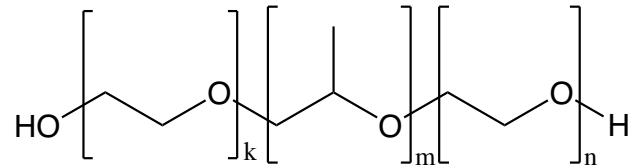
Ethylenediamine tetrakis(ethoxylate-block-propoxylate) tetrol (ETT)



Poly(ethylene glycol) (PEG)



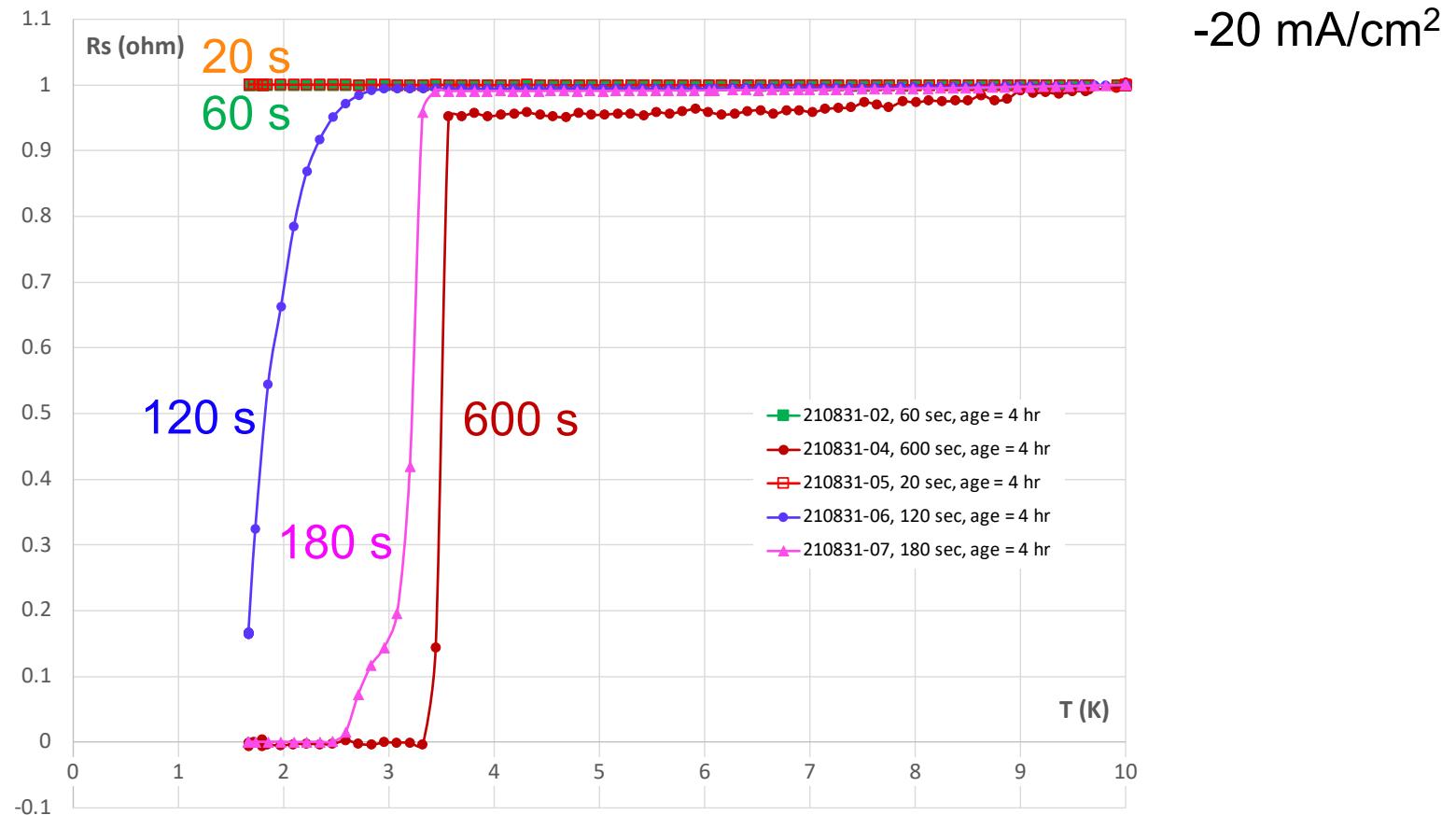
Poly(propylene glycol) (PPG)



Poly(ethylene glycol) – block – poly(propylene glycol) – block – poly(ethylene glycol) (PEG-PPG-PEG)

- The polymer branches are the critical groups.
- The hydrophobicity and molecular weight strongly impact the suppression effect.

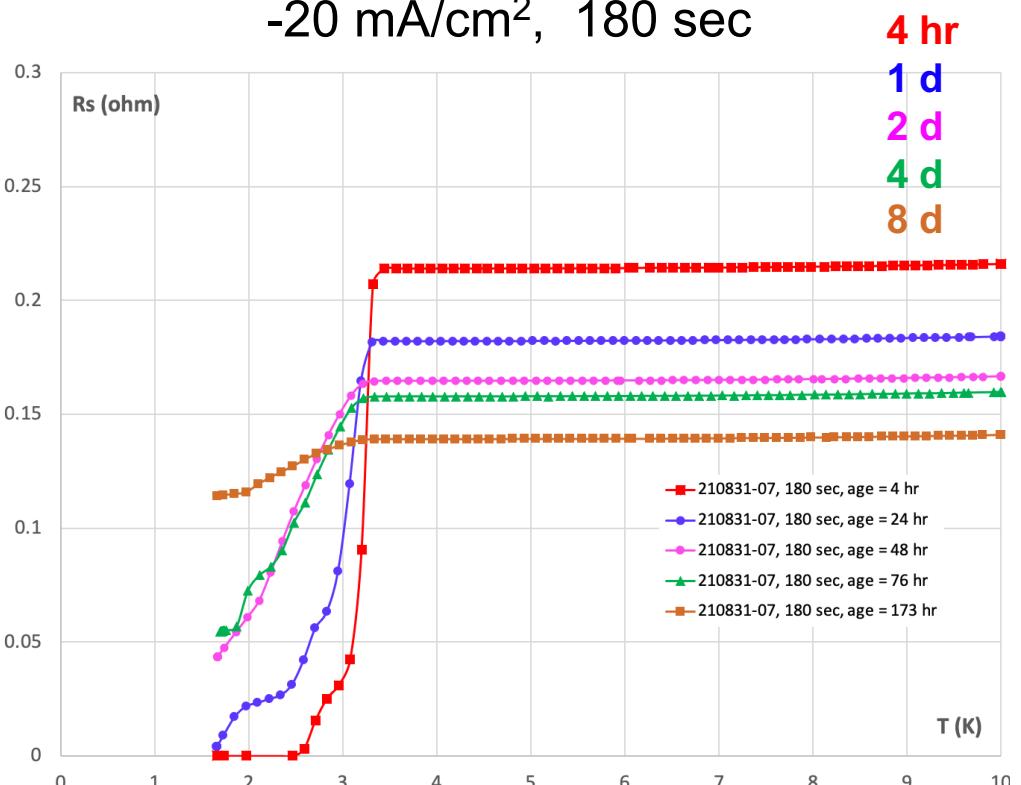
Film thickness on Superconductivity



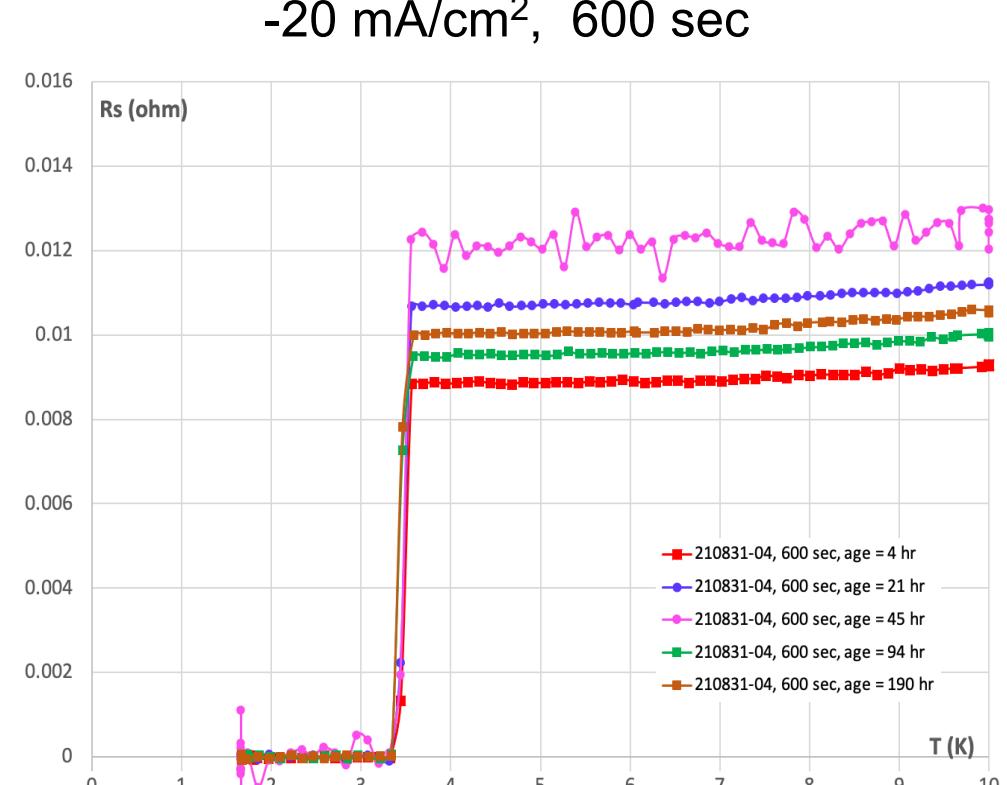
- The T_c of electrodeposited Sn on Au film decreases as the Sn thickness decreases.

Film aging on Superconductivity

-20 mA/cm², 180 sec



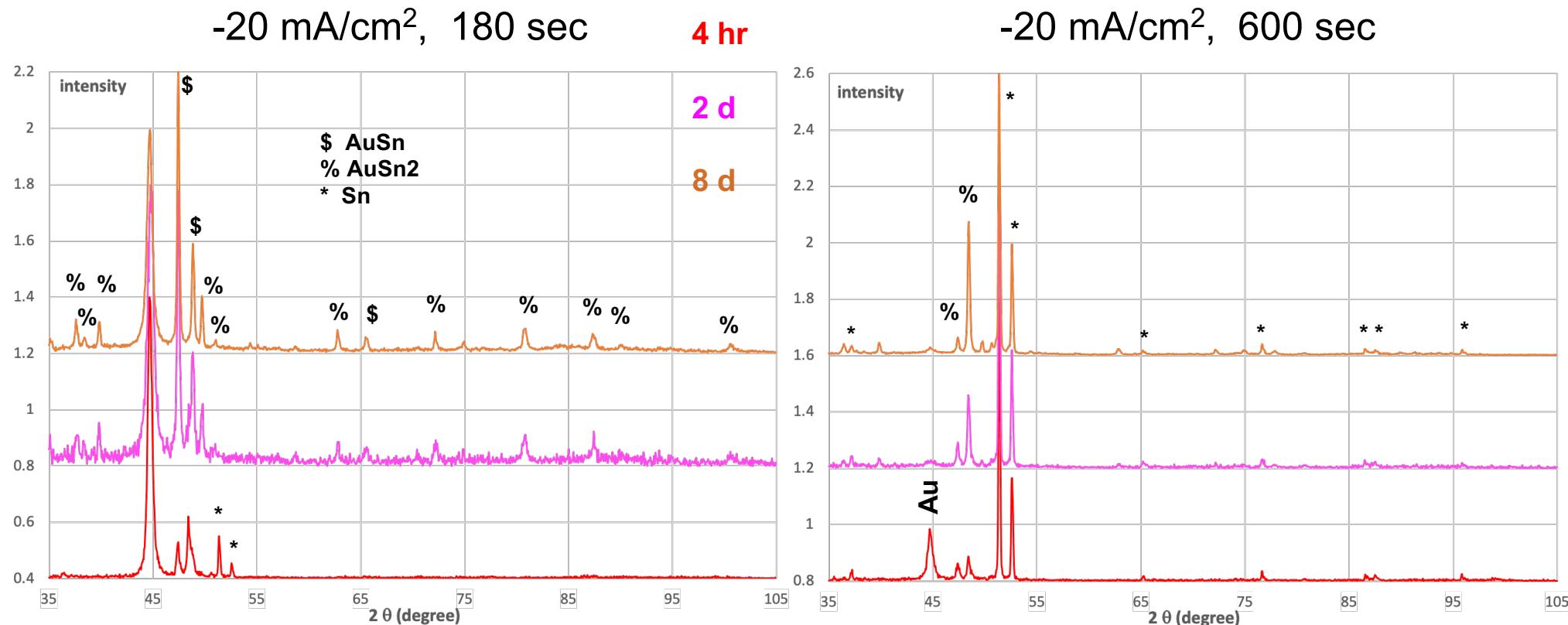
-20 mA/cm², 600 sec



- The T_c of electrodeposited thin Sn film on Au film decreases as Sn ages.

- Q. Huang, et al., *in preparation*, 2022.

Sn Film aging on Superconductivity

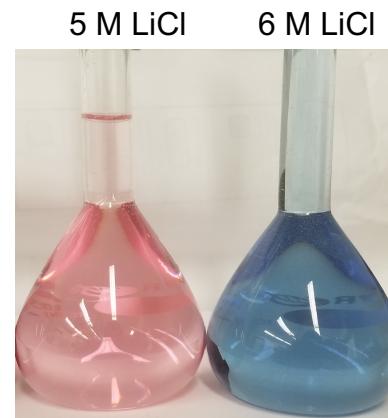
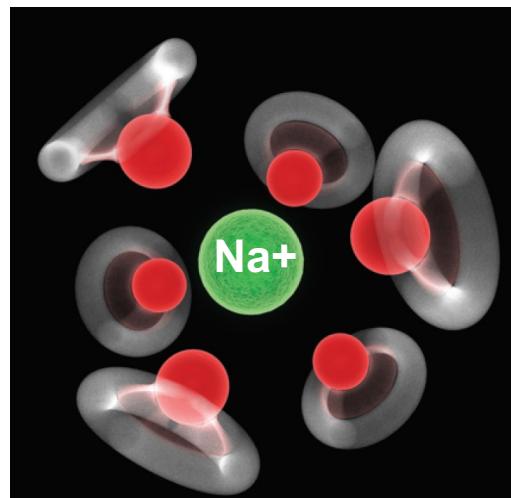
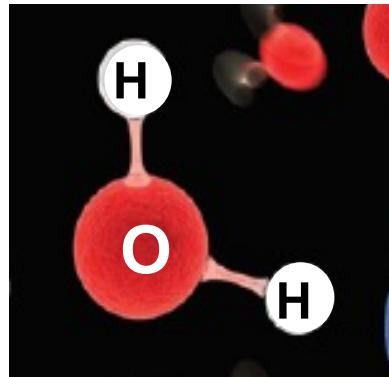
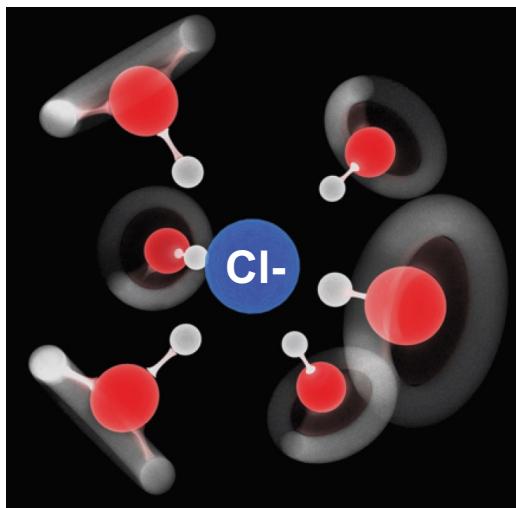


- No Au peaks observed for 600 sec Sn film after aging – completely consumed.
- No tetragonal Sn peak observed for 180 sec Sn film after aging – completely consumed.
- Tetragonal Sn still observed for 600 sec Sn after 8-day aging – consistent with the Tc.

Summary

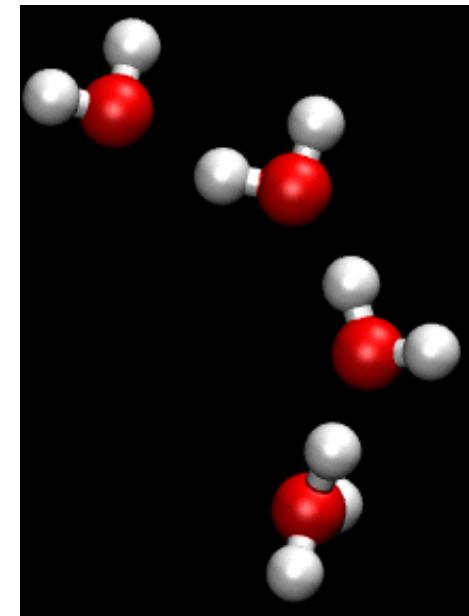
- **Organic additive for Sn electrodeposition to tune the nucleation and growth, as well as the superconducting transition.**
 - Hydrophobicity of additives dominates the adsorption and suppression effect
 - Adsorption dependent on not only the empty fraction but also the covered fraction.
 - Significant interdiffusion between Sn and Au occurs at room temperature, degrading the superconductivity upon aging.
- **Alkaline metal supporting salts and alloying metal cations in Re electrodeposition to tune the hydrogen evolution rate and alloy composition, as well as the superconducting transition.**

Hydration of Salts



- Laage et al., *J. Phys. Chem. B* (2009).

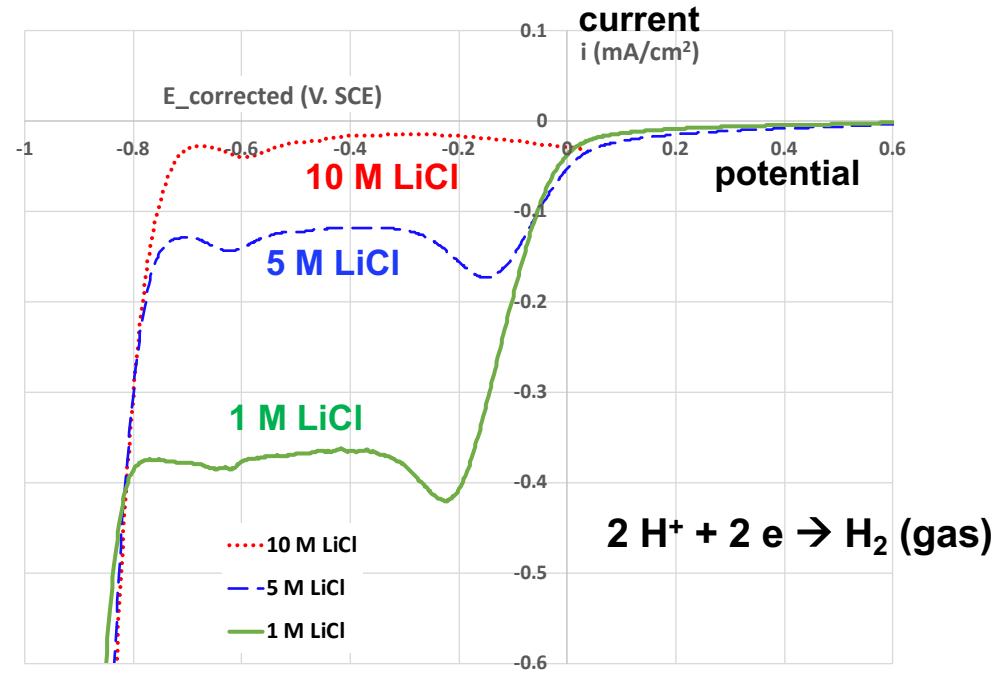
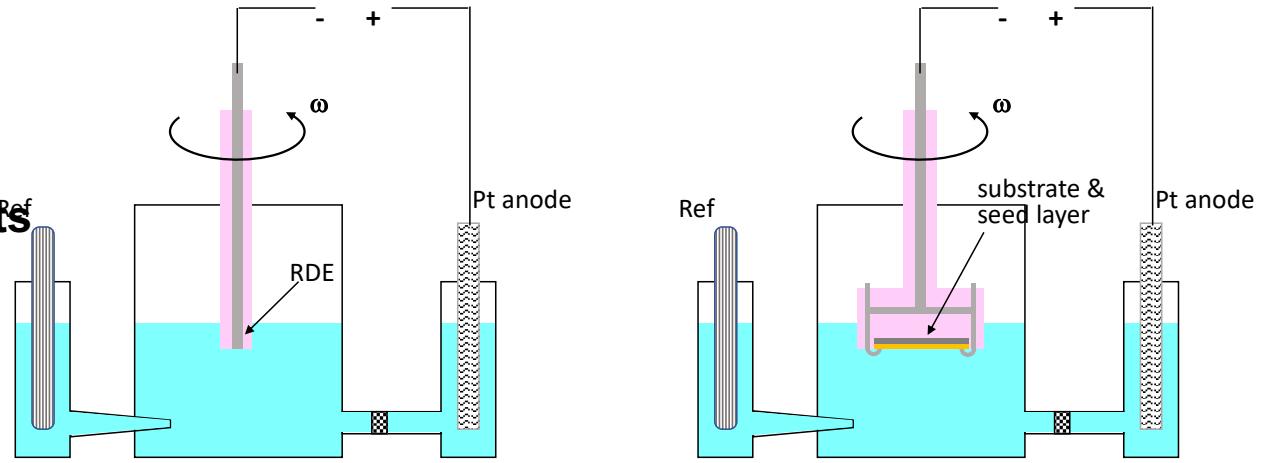
Grotthuss Mechanism
‘Proton Jumping’



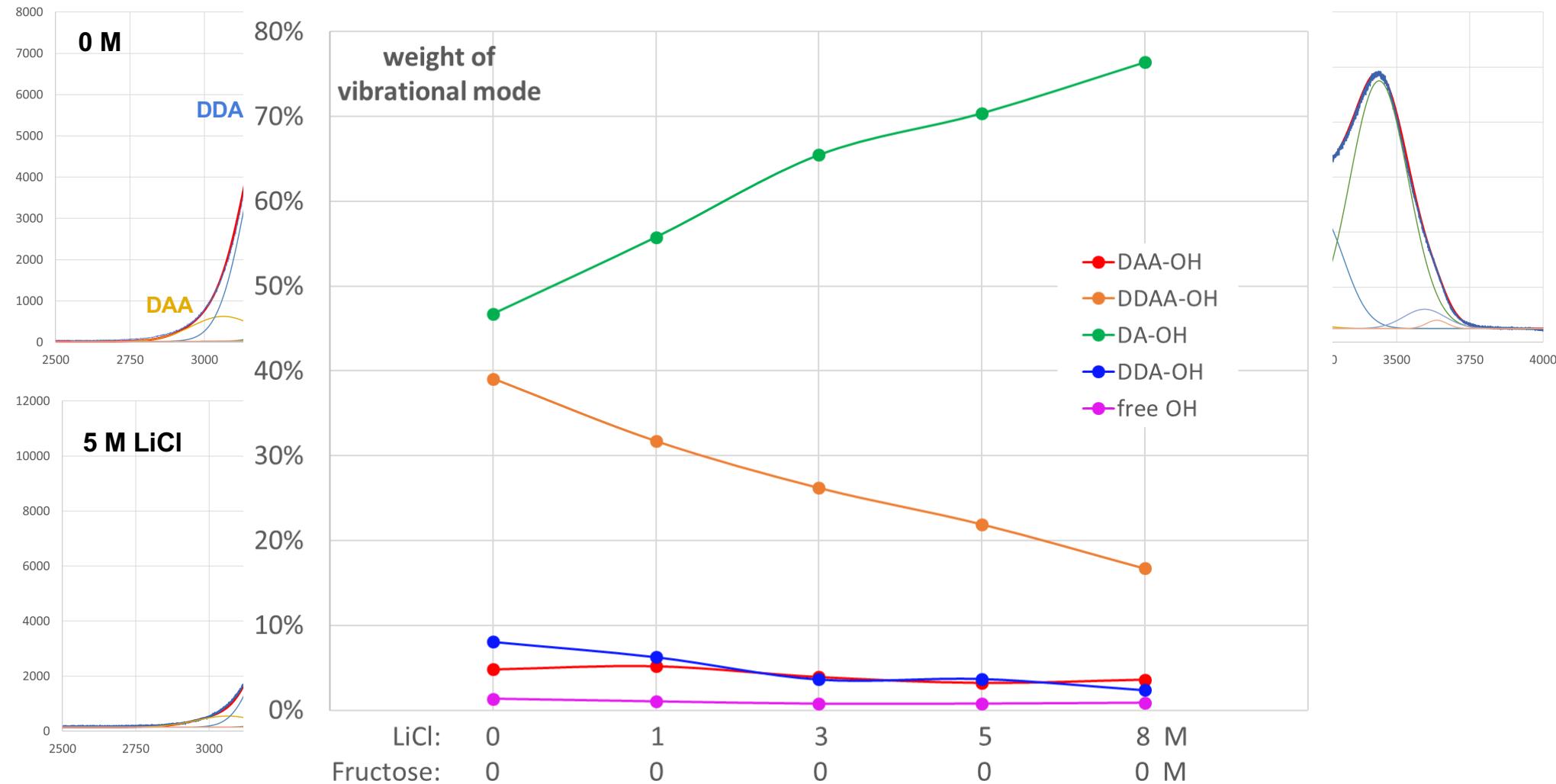
Matt K. Petersen
http://en.wikipedia.org/wiki/Grotthuss_mechanism

Electrodeposition of Re and alloys

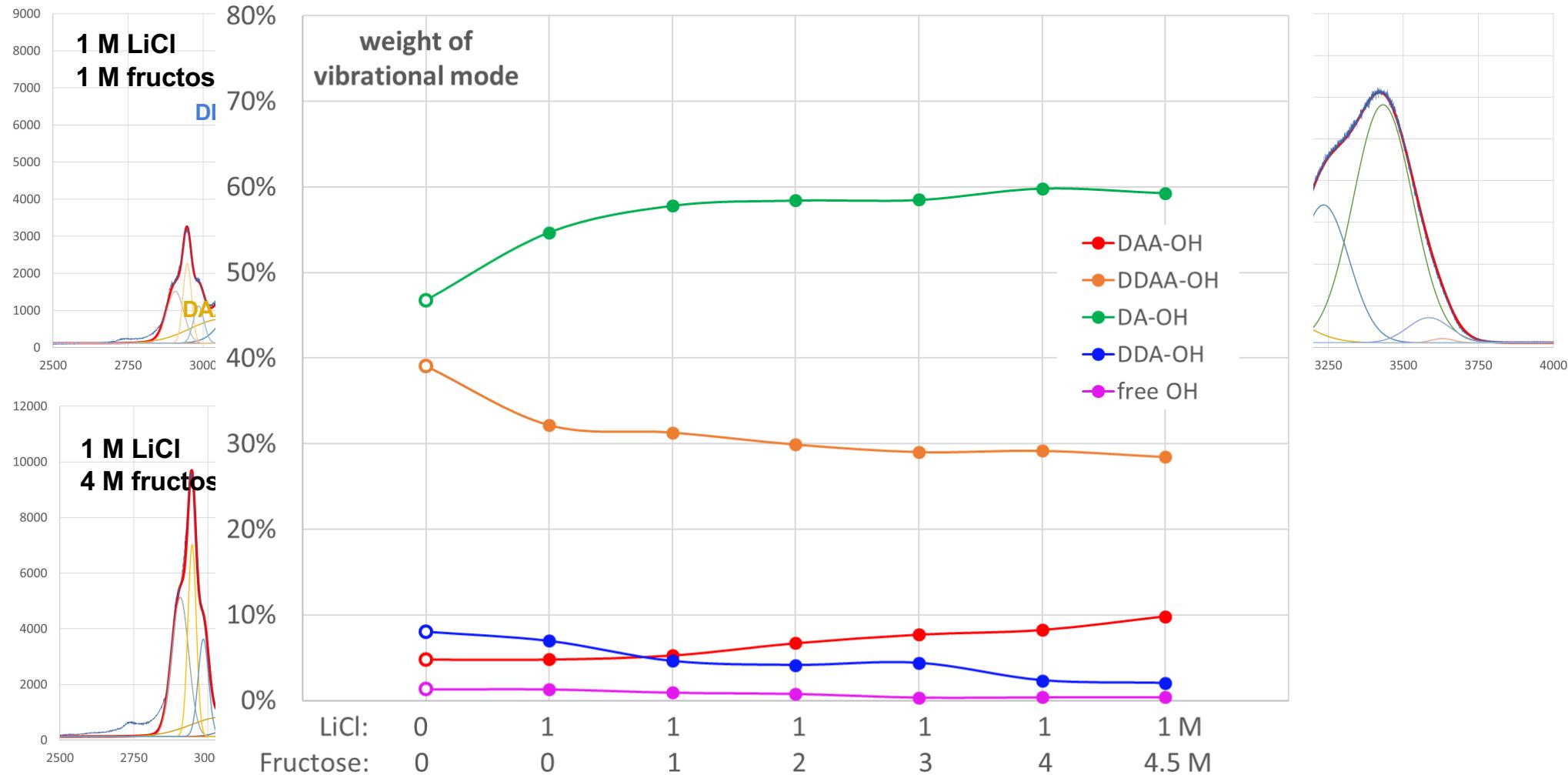
- NH_4ReO_4 0.025 M
- Alloying metal salts
- LiCl or other hydration salts
- Pt RDE
- Pt anode
- Ag/AgCl REF
- Si / SiO_2 / Ti / (100 nm) Au
- Characterization : XRF, SEM, XRD, PPMS, TEM, Raman



Hydration of LiCl



Hydration of organic solute



- Hydration of fructose (hydroxyl group) increases the viscosity, but not to disrupt the H-bond network as strongly as alkaline metal cations.

- Q. Huang, *J. Electrochem. Soc.*, 2022.

Hydration of different alkaline metal cations

Diffusion of H⁺ and acidity of solution

LiCl (M)	v (cm ² /sec)	D _H (cm ² /sec)	γ _H
1	0.01128	6.30E-5	1.412
3	0.01422	3.70E-5	1.457
5	0.01853	1.31E-5	1.981
8	0.03030	5.08E-6	2.254

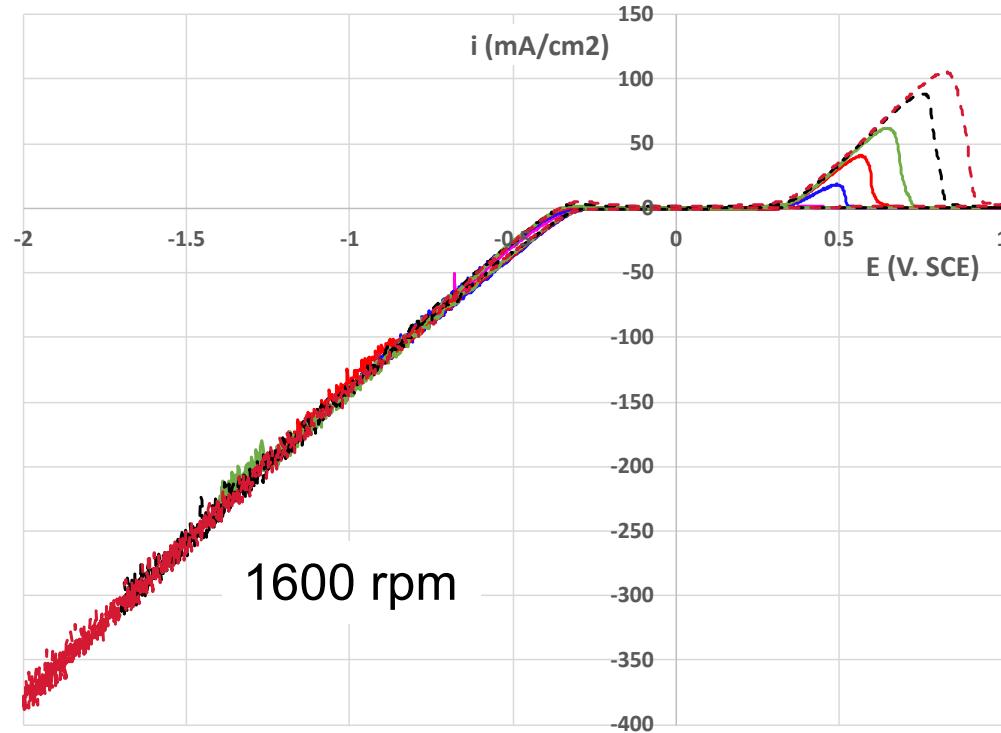
Salt	D _H (cm ² /sec)	γ _H
3 M LiCl	3.70E-5	1.457
3 M NaCl	4.43E-5	1.485
3 M KCl	6.42E-5	1.303
5 M LiCl	1.31E-5	1.981
5 M NaCl	3.31E-5	1.325

- H-bond network disruption : Li⁺ > Na⁺ > K⁺.

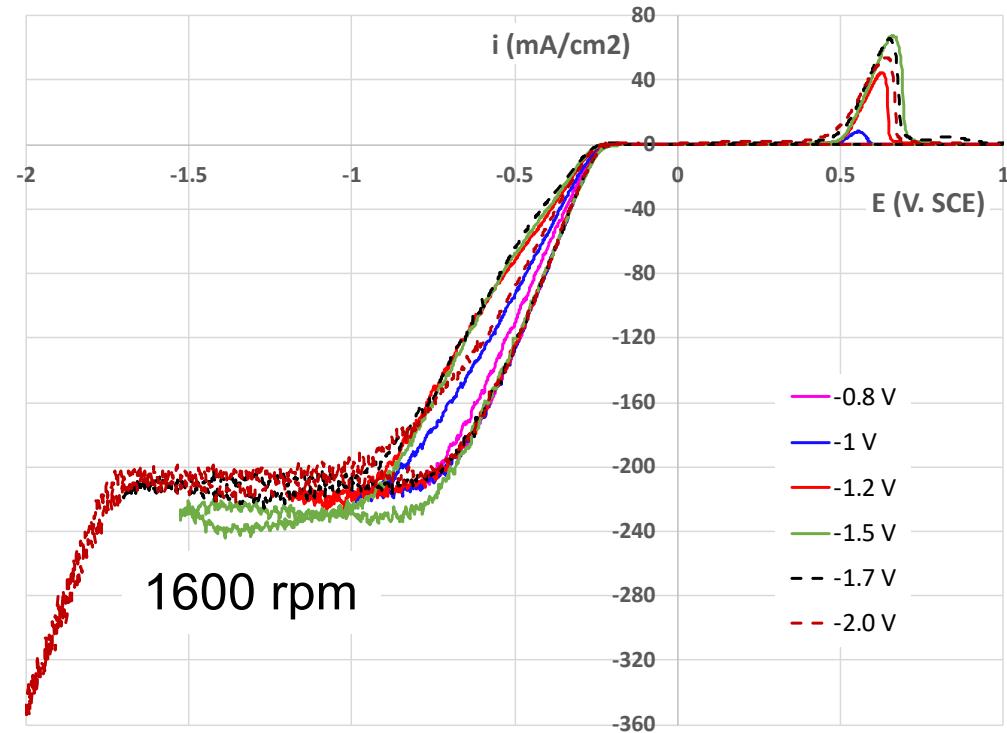
- S. De, *Electrochim. Acta.*, 2020.

Water-in-Salt for Re deposition

0.025 M NH_4ReO_4 , 0.1 M H_2SO_4



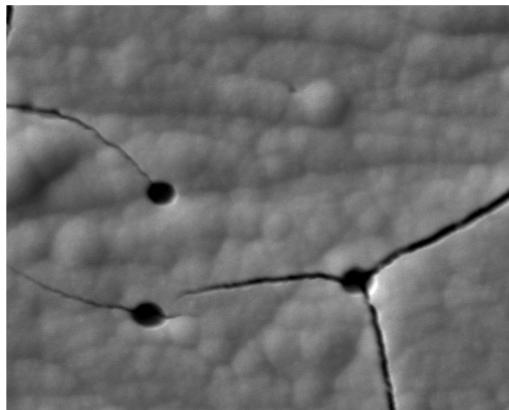
0.025 M NH_4ReO_4 , 0.1 M H_2SO_4 , 5 M LiCl



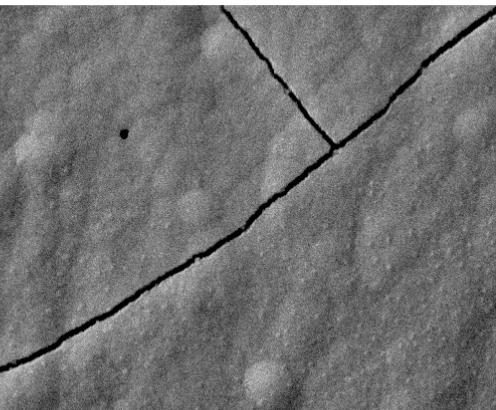
- Q. Huang, T. Lyons, *Electrochim. Comm.*, 2018.

Re morphology

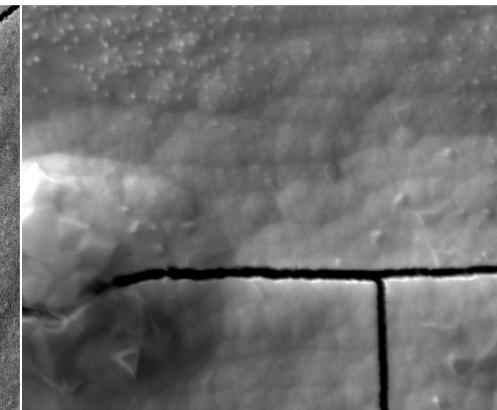
-100 mA/cm², 600 sec



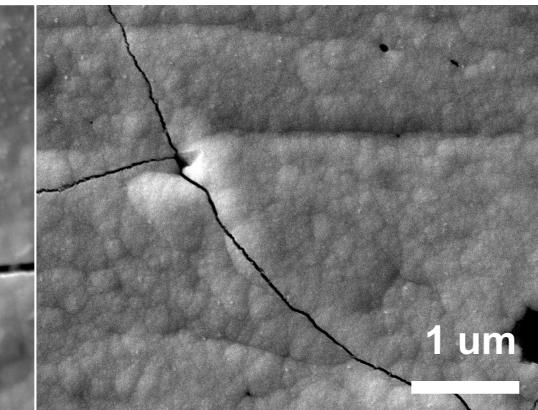
-150 mA/cm², 600 sec



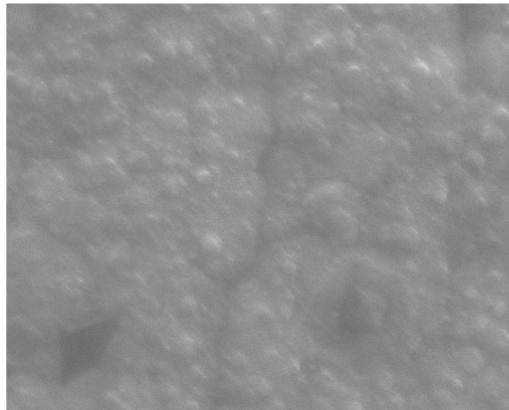
-200 mA/cm², 300 sec



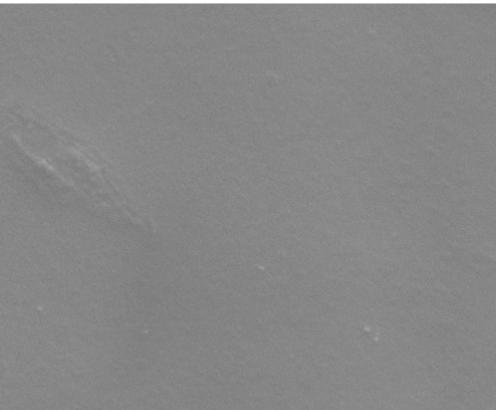
-250 mA/cm², 200 sec



-0.9 V, 900 sec



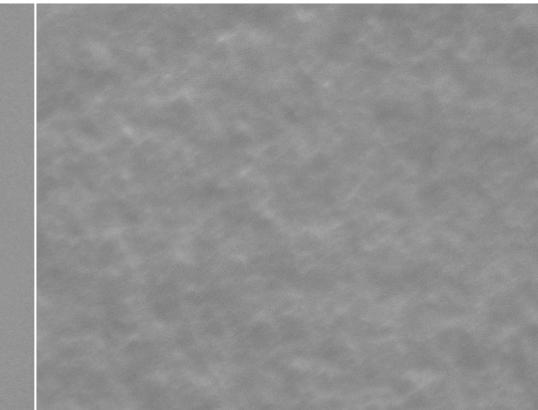
-1 V, 900 sec



-1.1 V, 600 sec

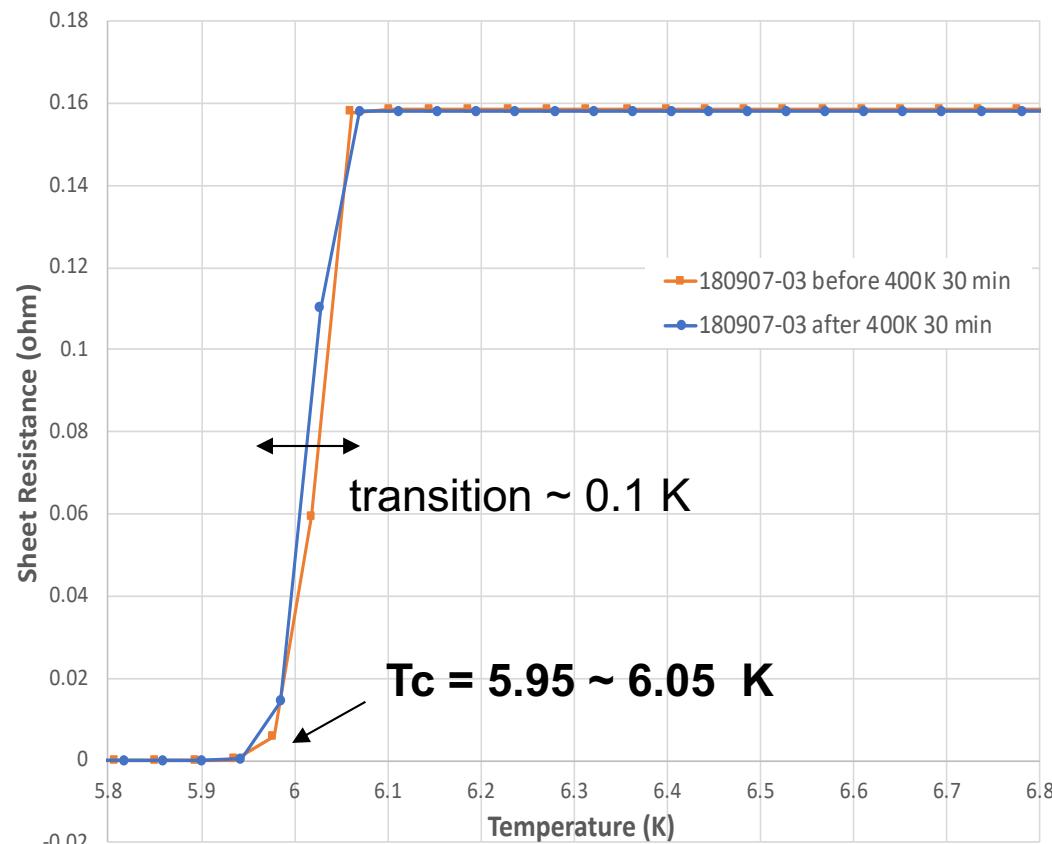
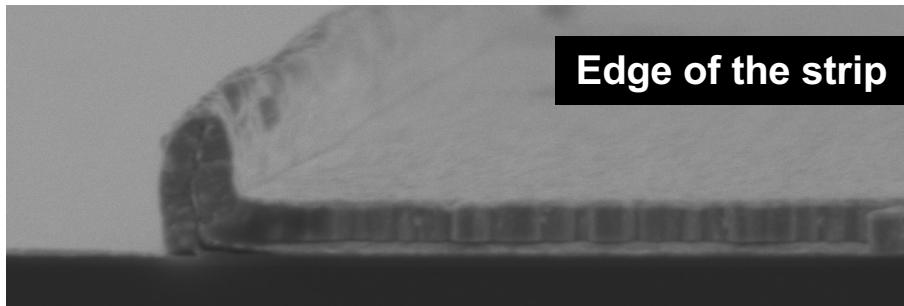
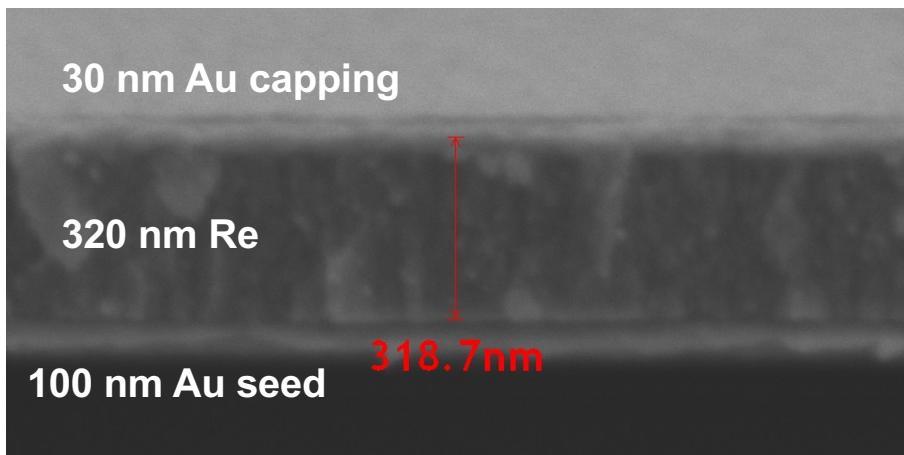


-1.2 V, 600 sec



- Q. Huang, Y. Hu, *J. Electrochem. Soc.*, 2018.

XSEM & Superconductivity



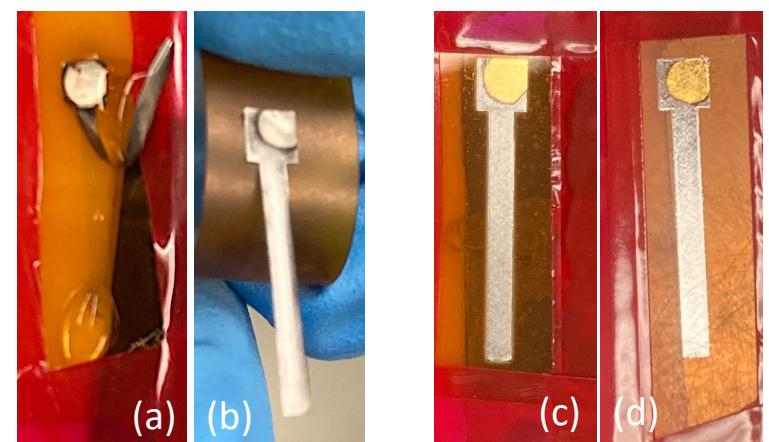
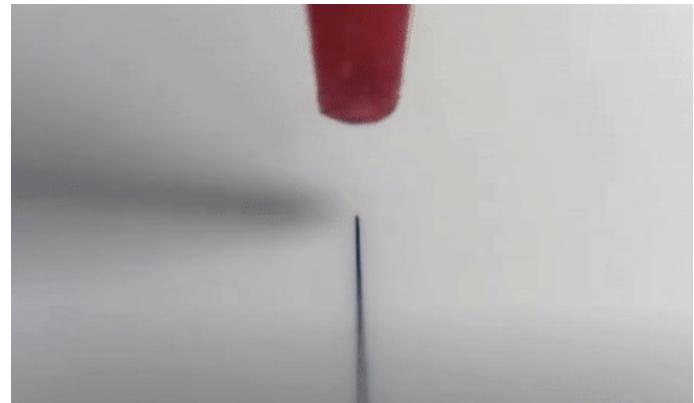
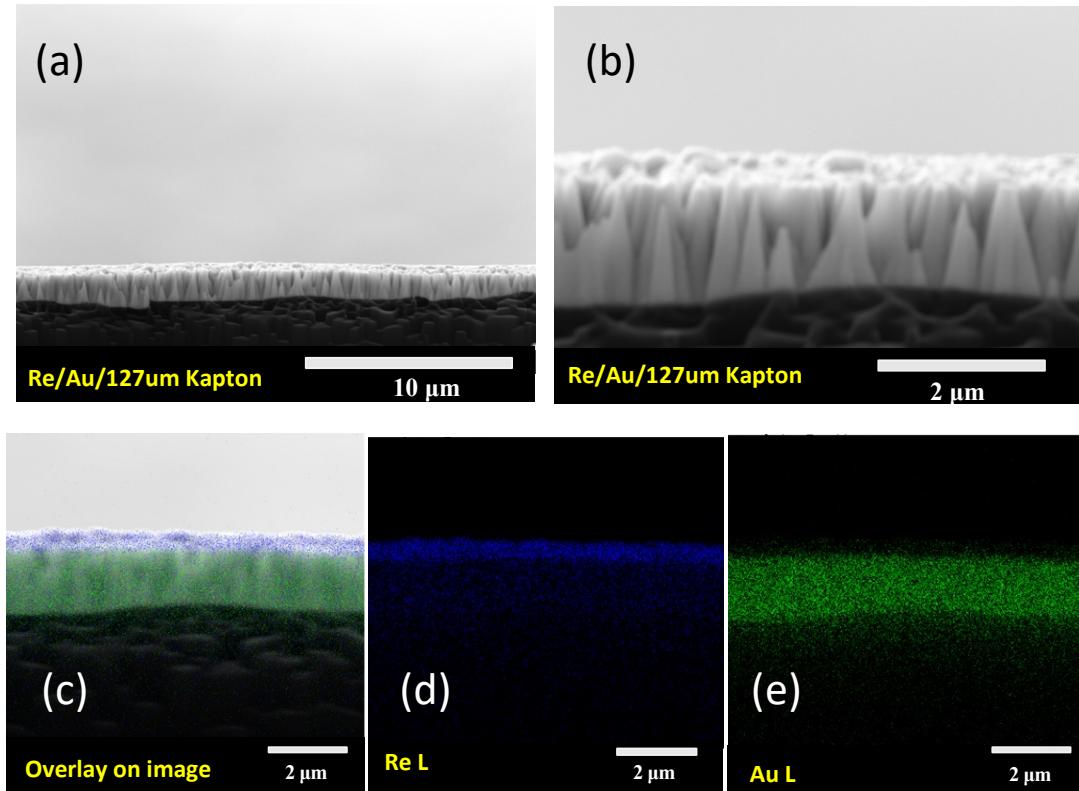
- Q. Huang, Y. Hu, *J. Electrochem. Soc.*, 2018.

- Enhanced T_c of 6 K was obtained for as deposited amorphous Re film, as compared with 1.7 K for bulk crystalline Re.

Electrodeposition of Re for flexible connector

Late E-2504 - Digital Presentation, by L. Tsui

- Aerosol Jet Printing of metal seed followed by Re electrodeposition

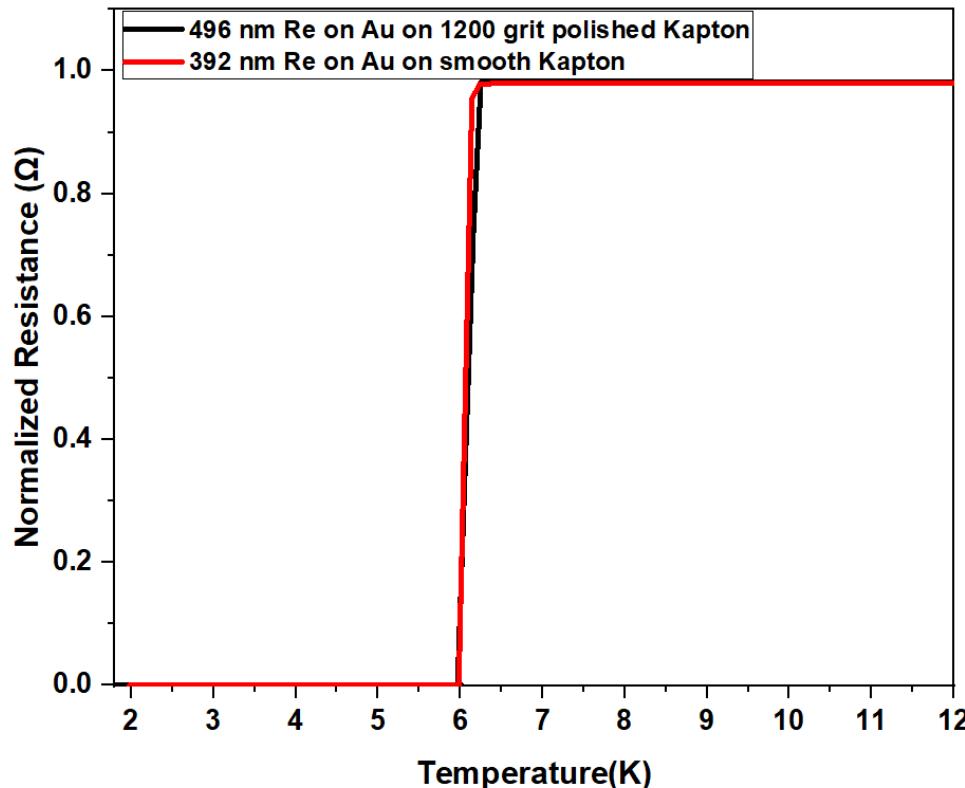


- Columnar grains observed for AJP Au, clear interface between Kapton / Au / Re.
- Adhesion strongly depends on the AJP metal, poor adhesion for Ag.

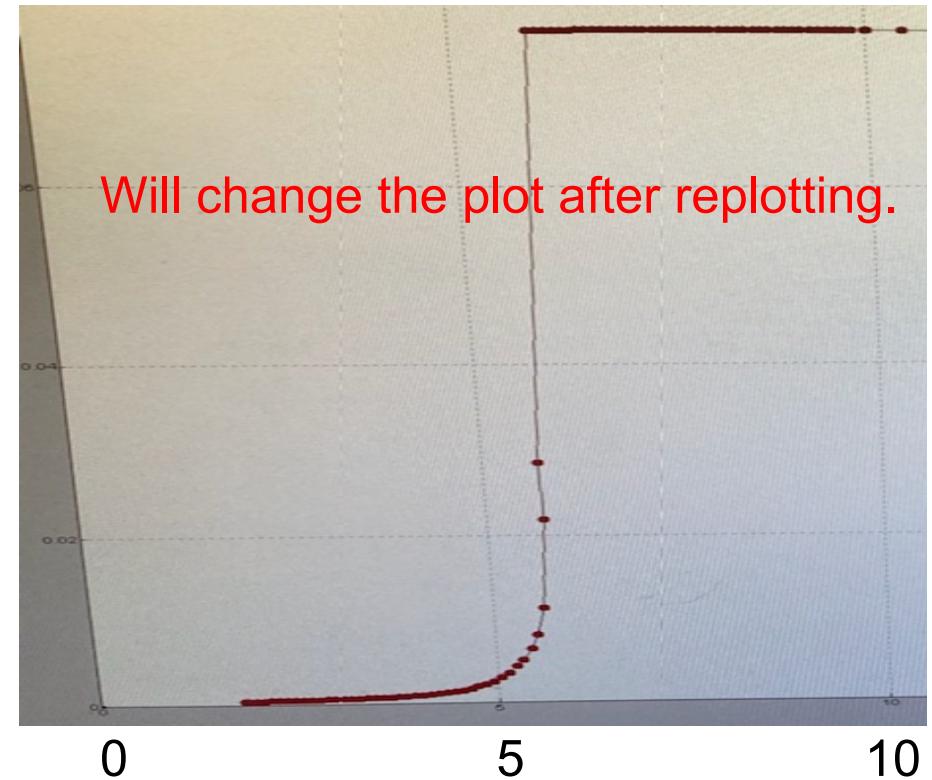
Electrodeposition of Re for flexible connector

Late E-2504 - Digital Presentation, by L. Tsui

Typical as deposited Re film



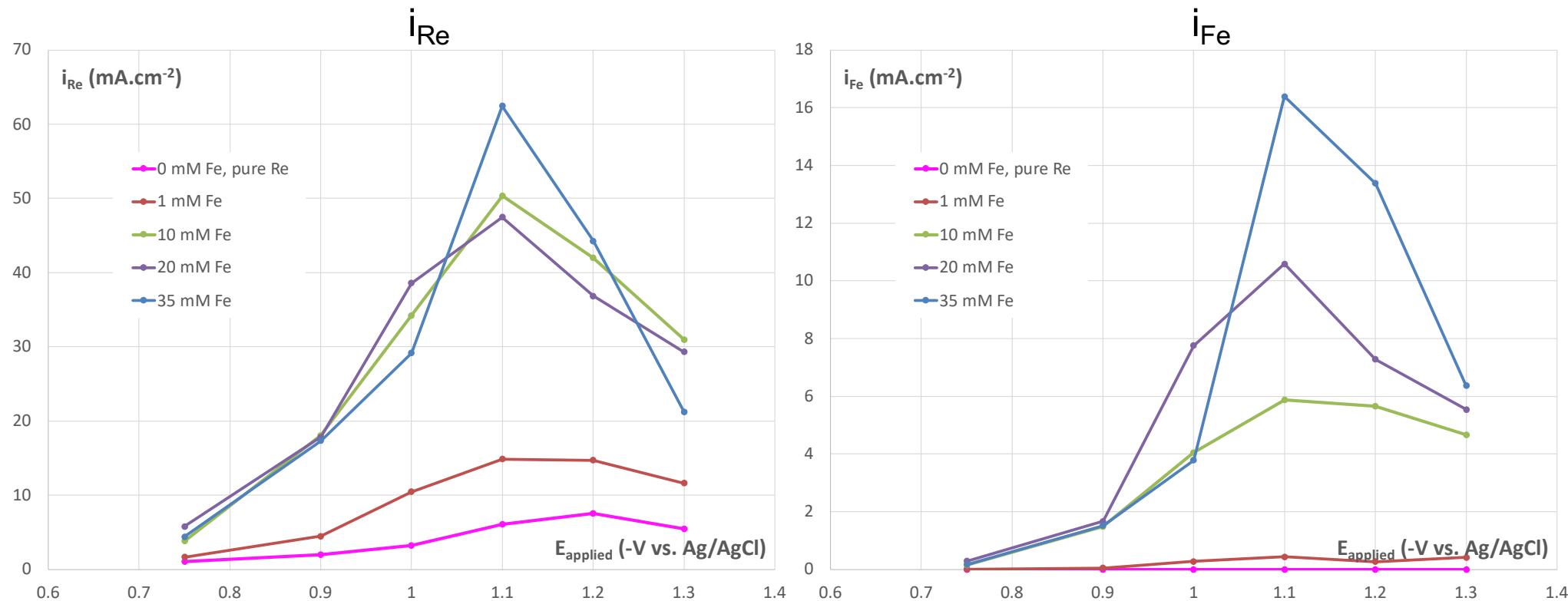
After flexure of 200 cycles



- Improved T_c of 6 K (as compared with 1.7 K for crystalline Re) is demonstrated on AJP Au on Kapton, consistent with results on silicon coupons.
- Flexure for 200 cycles did not significantly alter the T_c , small tail observed is believed to relate to corrosion of Re.

- K. Ahammed, et al, *in preparation*, 2022.

Effect of Fe & Co on Re deposition

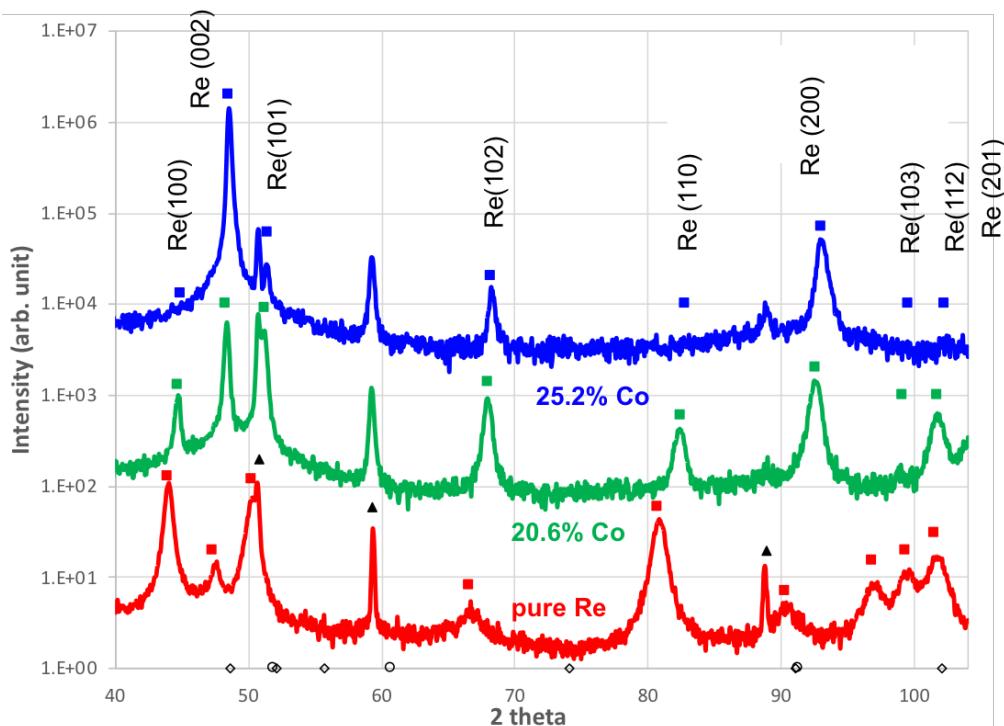


- The presence of Fe^{2+} promotes the Re deposition rate, up to 10 times faster.
- Presence of Co^{2+} also promotes Re deposition, but the effect is less pronounced.

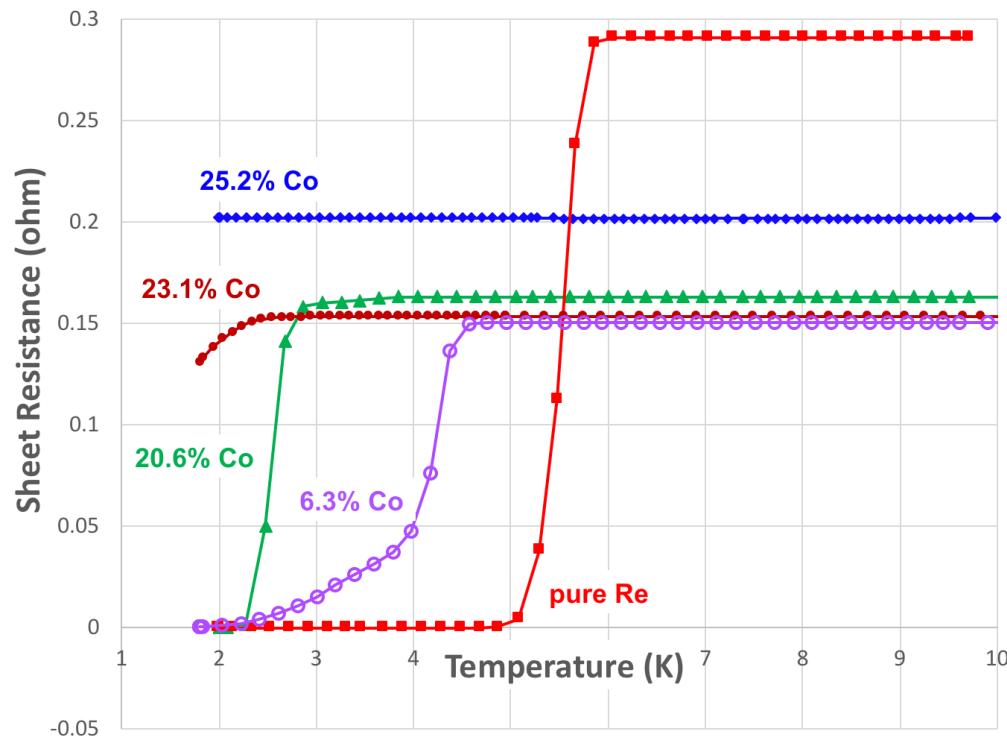
- B. Malekpouri, Q. Huang, *J. Alloy Comp.*, 2022.

Effect of Co alloying

vacuum 200 C 30 min



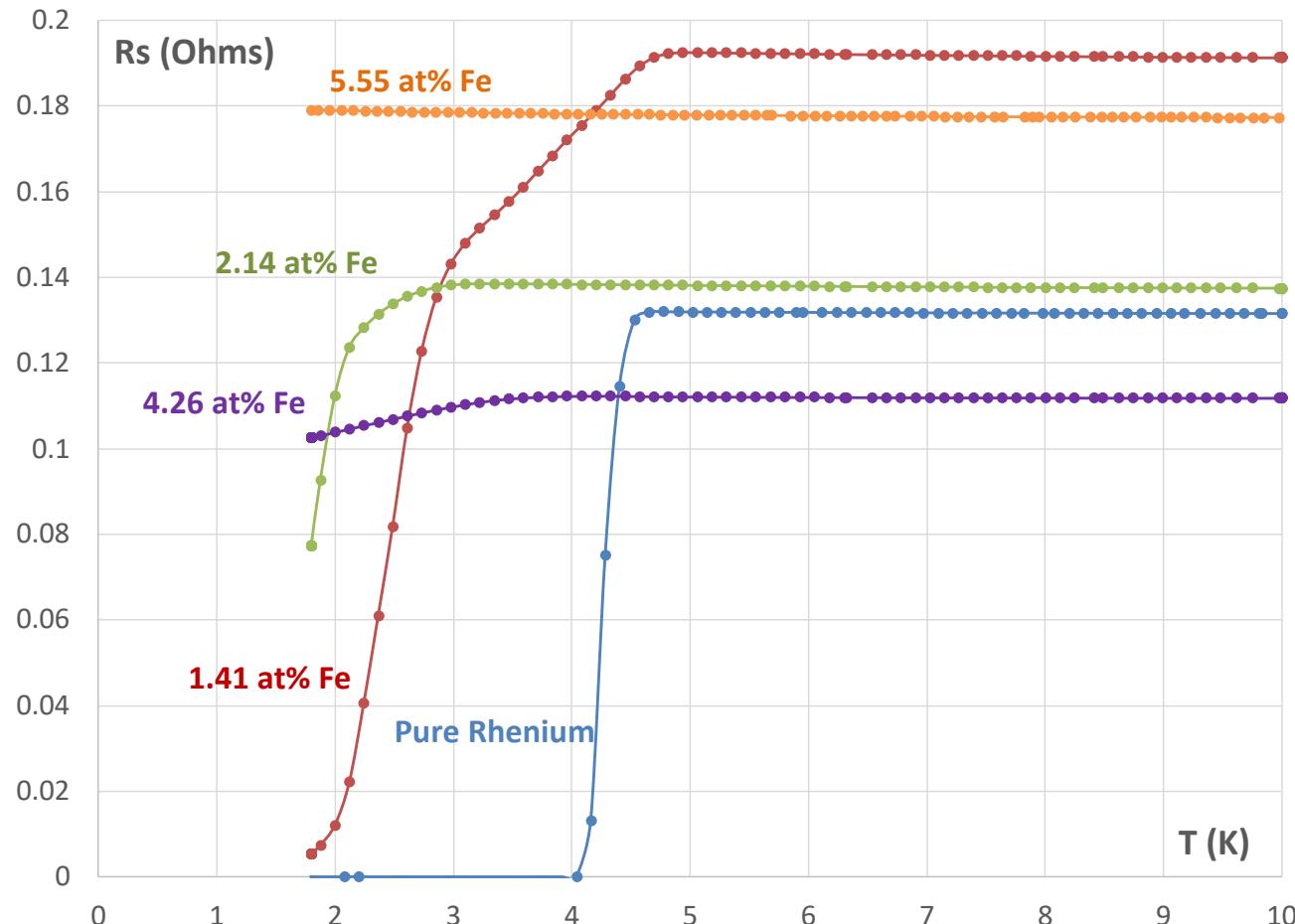
T_c before annealing



- S. De, et al., *J. Electroanal. Chem.*, 2020.

- T_c gradually decreases upon alloying of Co into Re.
- As deposited ReCo alloys are amorphous, films re-crystallizes upon 200 C anneal.
- HCP single phase solid solution can be obtained for ReCo after annealing.

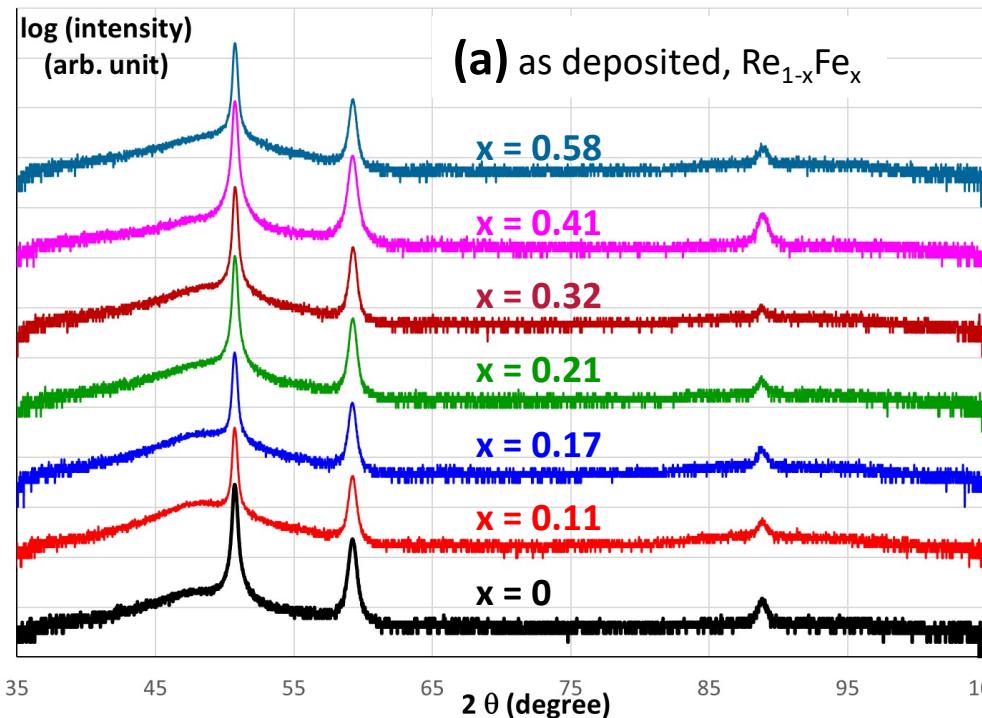
Effect of Fe on Tc



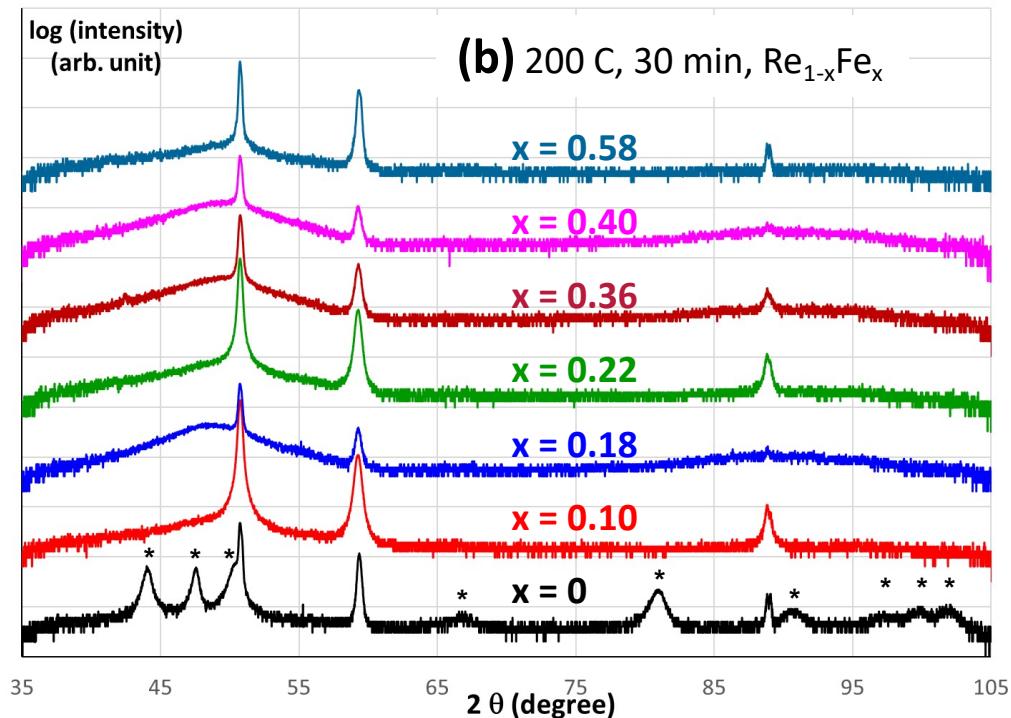
- Alloying with Fe also decreases the Tc of Re, and the effect is much stronger than Co.

Effect of Fe on Re recrystallization

As deposited



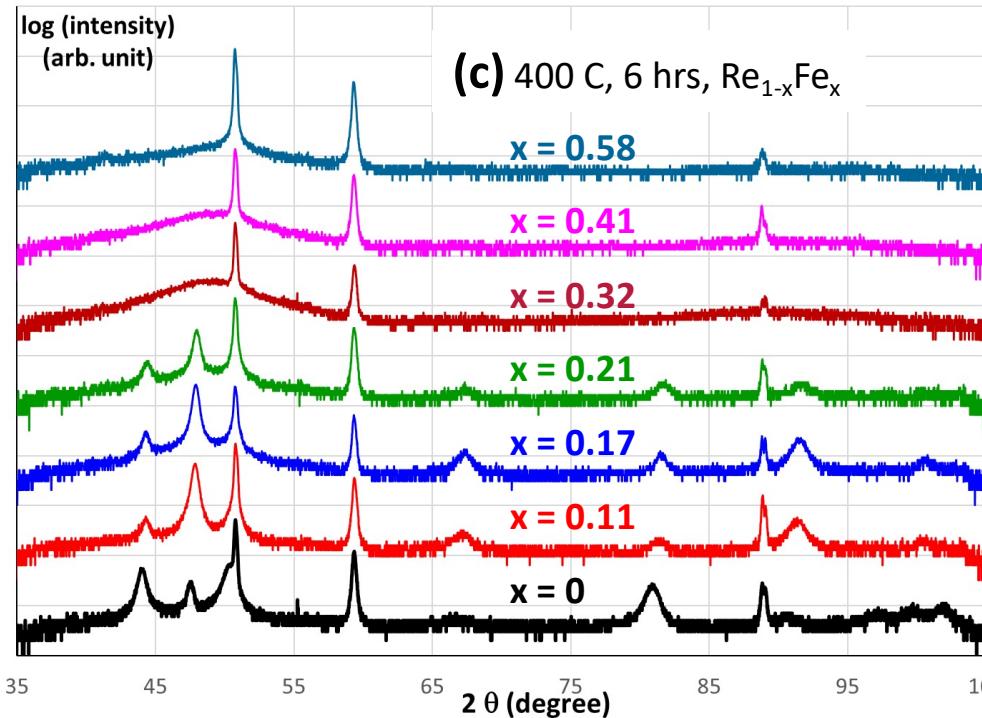
vacuum 200 C 30 min



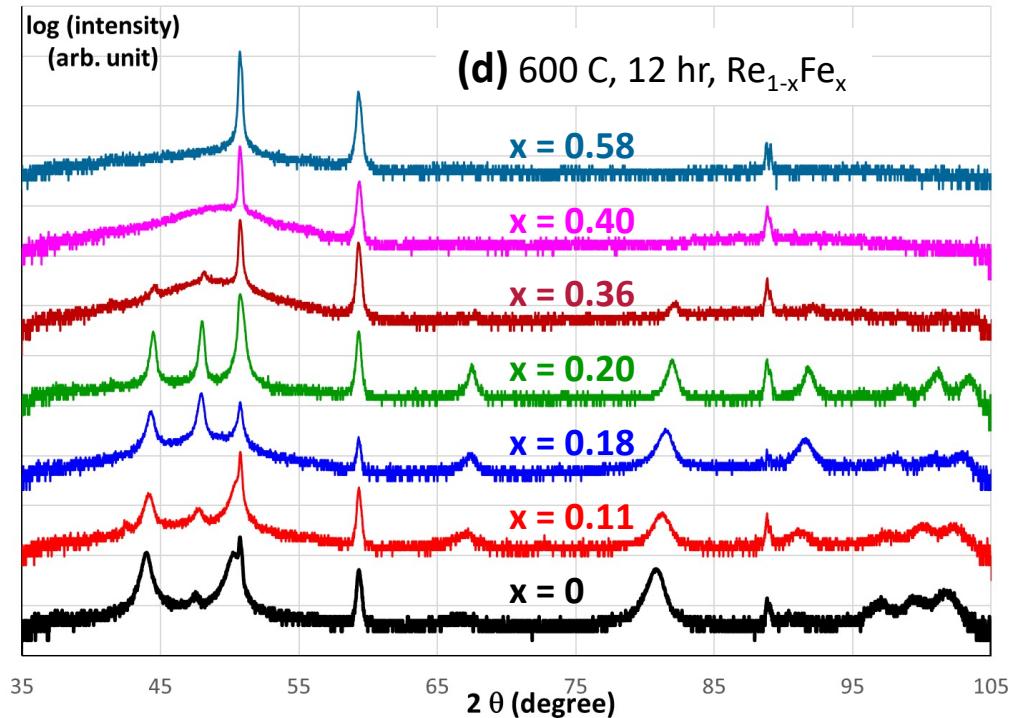
- As deposited ReCo alloys are amorphous, 10% Fe prevents the film from re-crystallization at 200 C.

Effect of Fe on Re recrystallization

vacuum 400 C 30 min



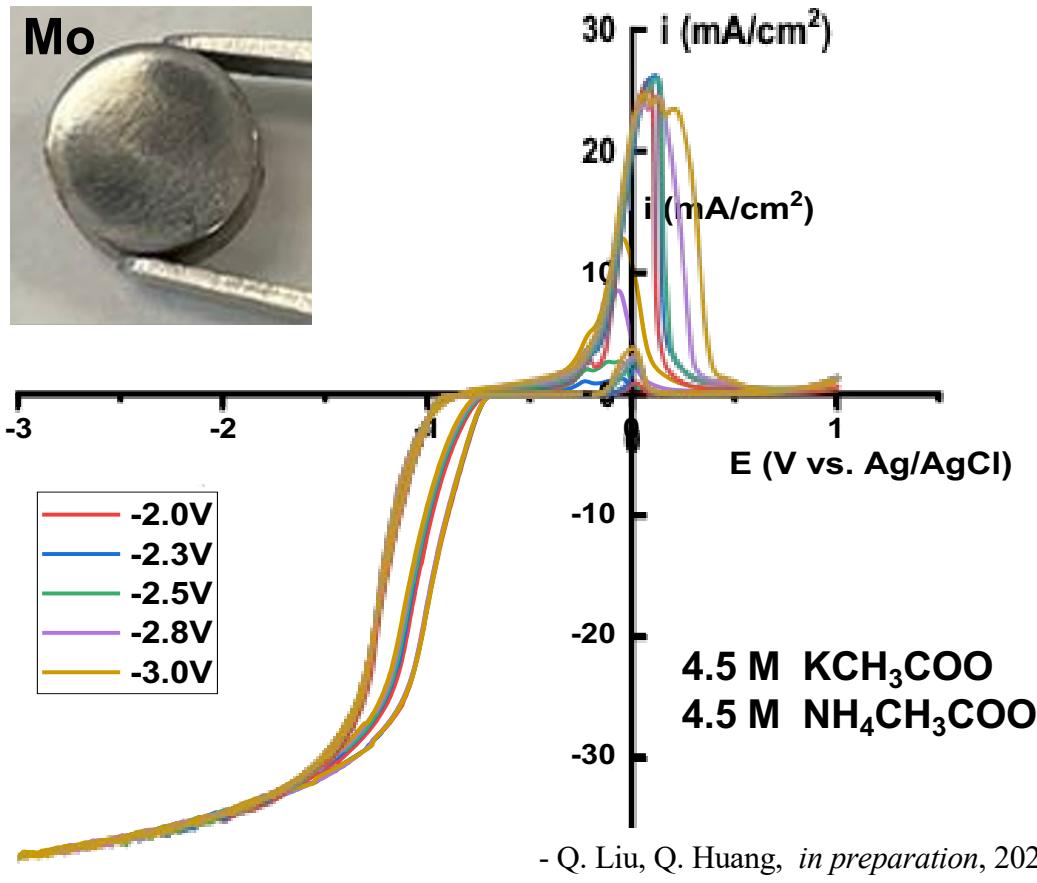
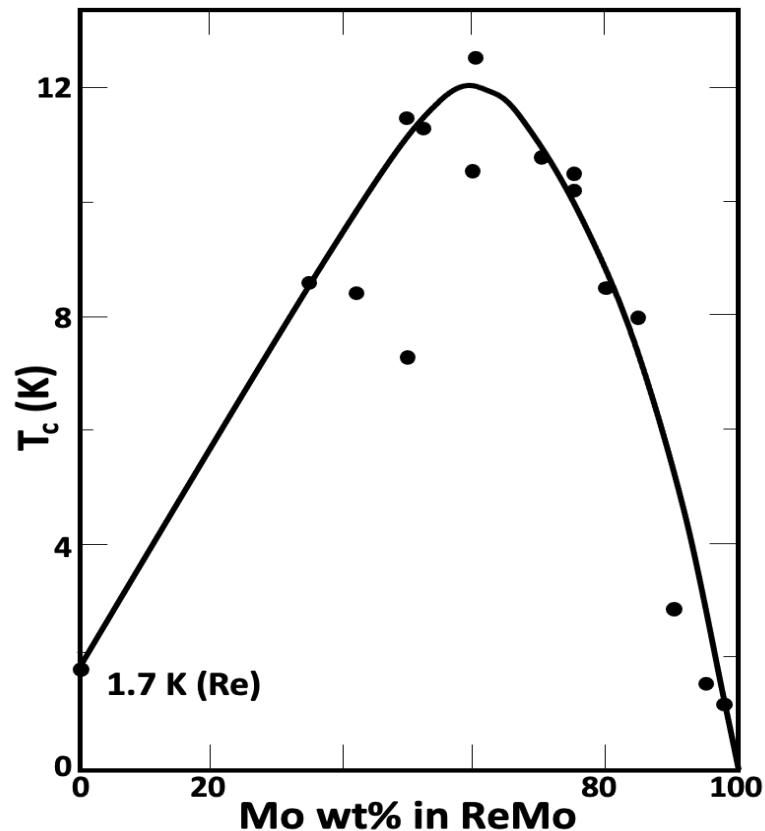
vacuum 600 C 30 min

- B. Malekpouri, Q. Huang, *J. Alloy Comp.*, 2022.

- Higher temperature annealing enables the recrystallization of films with higher Fe%.
- 600 C annealing is not able to crystallize films with 40+ % Fe.

Electrodeposition of Mo from Aqueous solution

Late E-2536 – Poster, by Q. Liu

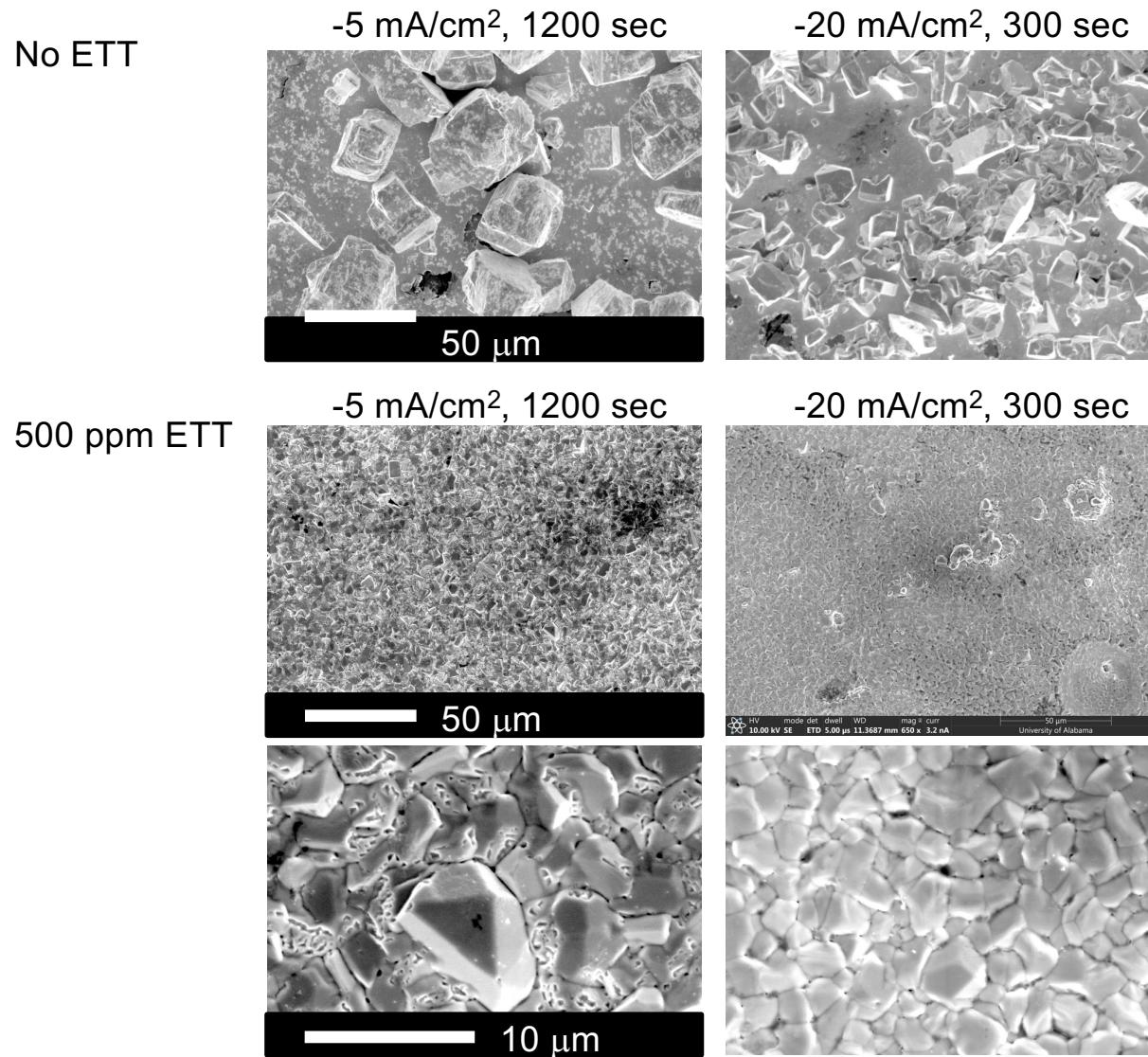


- Q. Liu, Q. Huang, *in preparation*, 2022.

- Metallic Mo obtained from super high concentrate acetate solutions
- K^+ is necessary for Mo deposition, and the Mo deposition rate increases with K^+ concentration
- Substrate makes big difference – also suggesting HER inhibits Mo deposition.

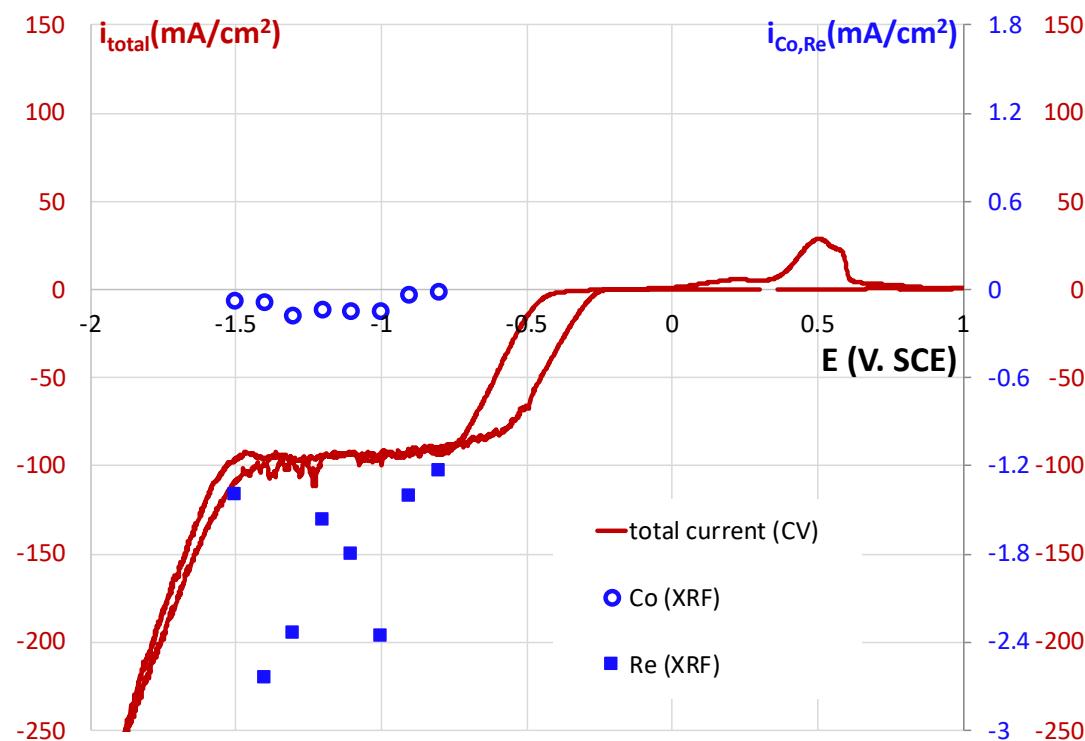
Summary

- **Organic additive for Sn electrodeposition to tune the nucleation and growth, as well as the superconducting transition.**
 - Hydrophobicity of additives dominates the adsorption and suppression effect
 - Adsorption dependent on not only the empty fraction but also the covered fraction.
 - Significant interdiffusion between Sn and Au occurs at room temperature, degrading the superconductivity upon aging.
- **Alkaline metal supporting salts and alloying metal cations in Re electrodeposition to tune the hydrogen evolution rate and alloy composition, as well as the superconducting transition.**
 - Deposition of superconducting Re demonstrated on flexible substrates
 - Iron group metals failed to improve T_c , but to degrade the T_c
 - Mo deposition was demonstrated from Water-in-Salt, with strong substrate effects.

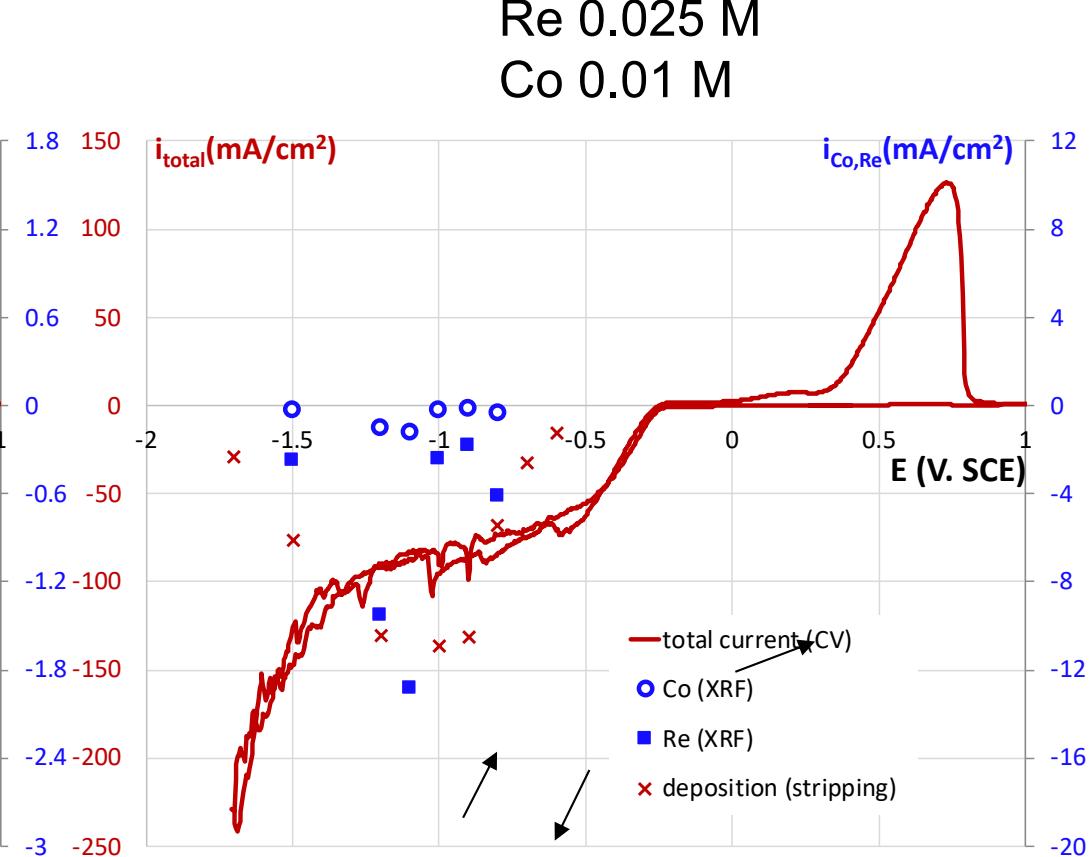


Back up – Co on Re

Re 0.025 M
Co 0.001 M

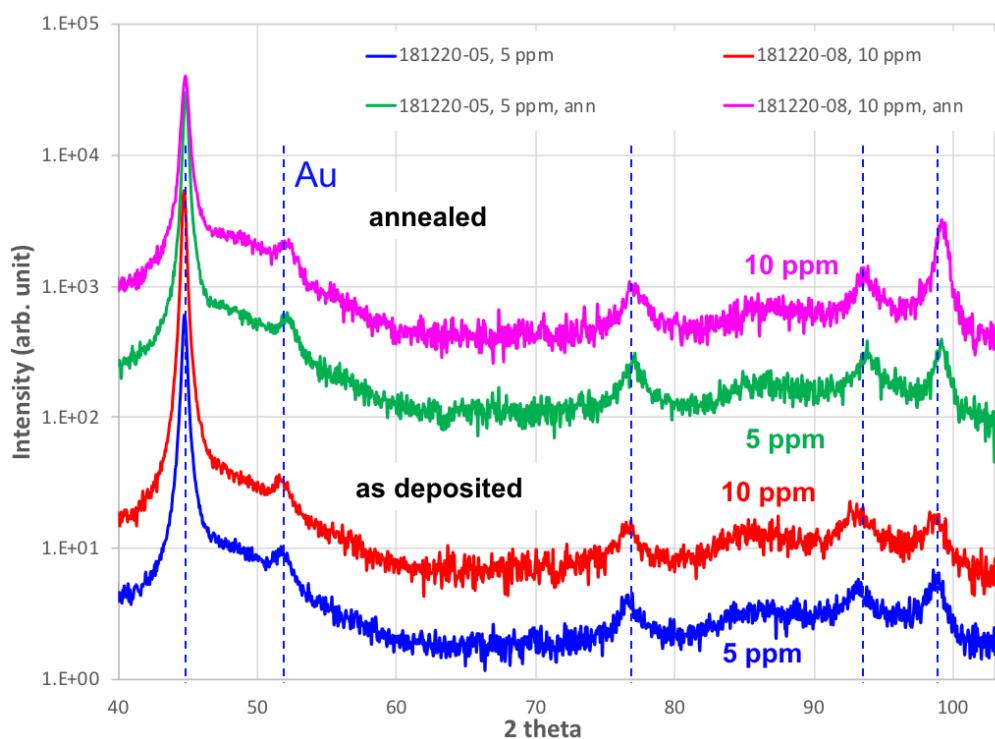


Re 0.025 M
Co 0.01 M

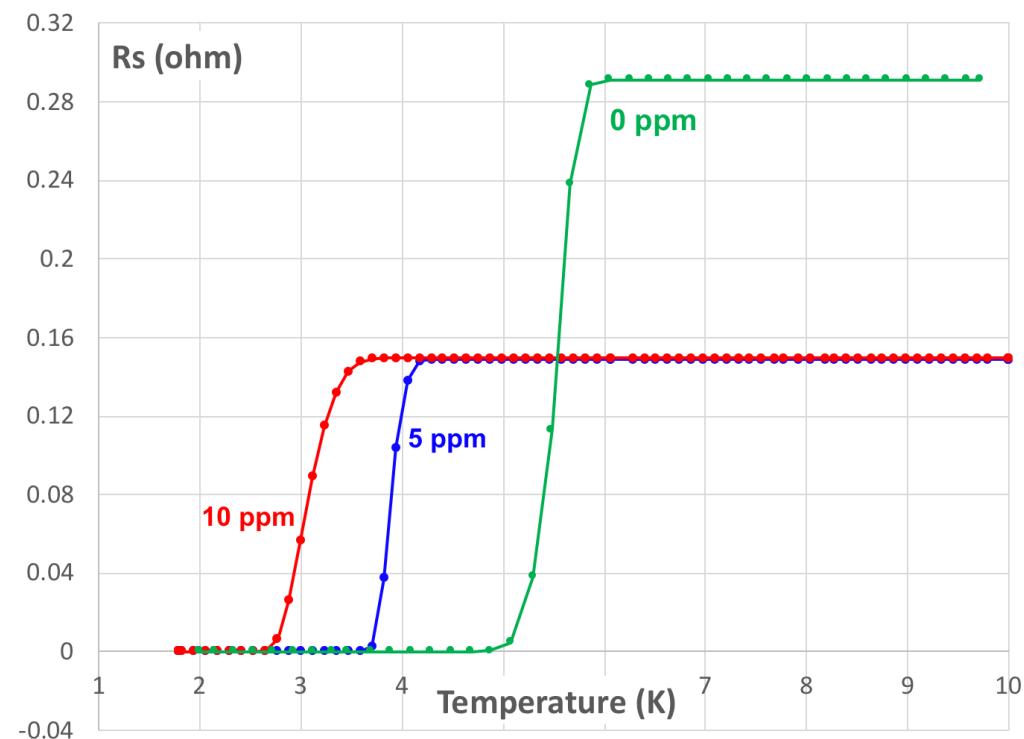


S doping (thiourea)

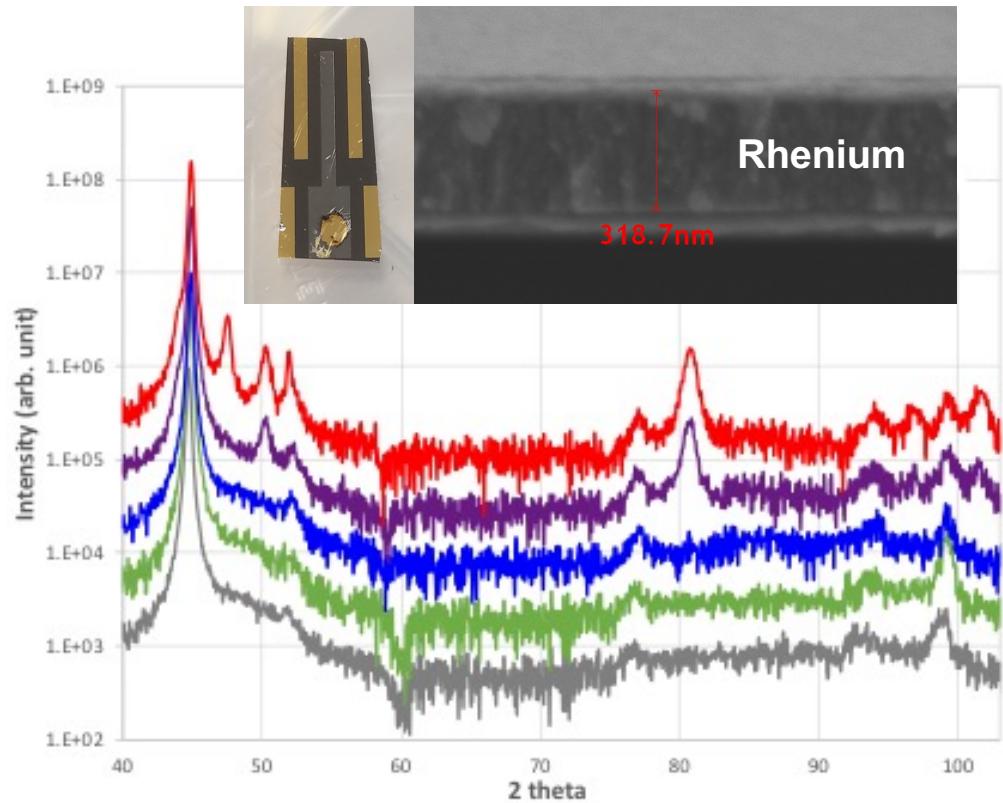
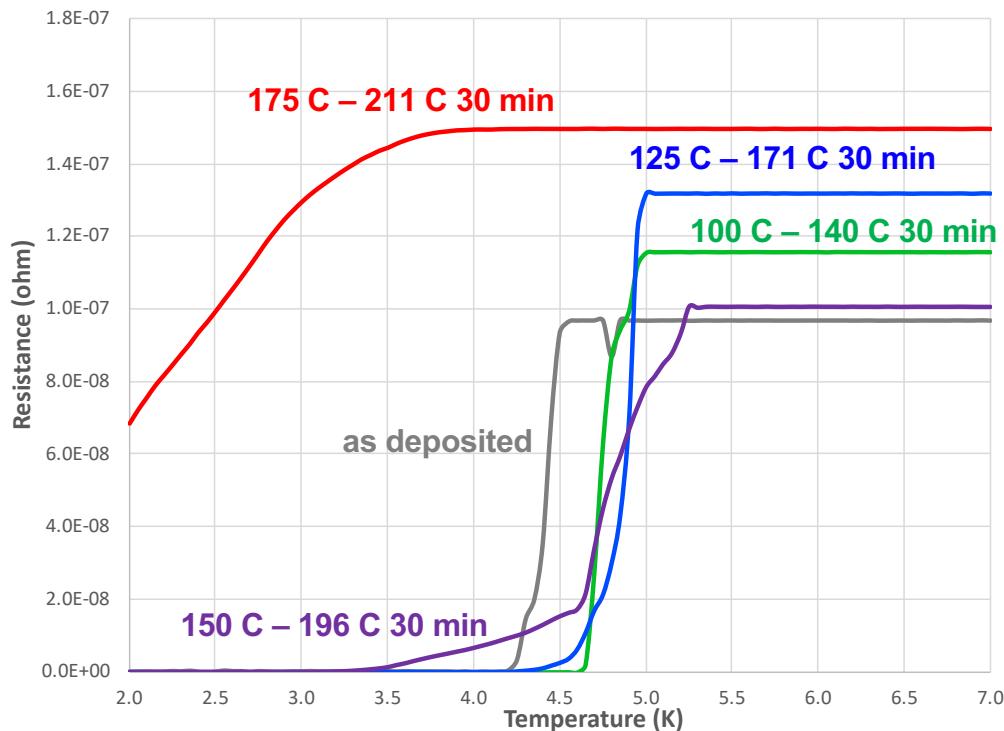
vacuum 200 C 30 min



T_c before annealing



Back up – crystallization of Re



- Sides & Huang, *J. Appl. Phys.*, 2020.

- Recrystallization of as-deposited amorphous Rhenium film results in degradation of superconductivity.
- Critical temperature above He boiling point (4.2 K) is desired for connector application.